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Nanotechnology: A Look into the Future

Topics ...

- **Why is IBM pursuing research in nanoscale science and technology?**
- **Self-assembly - the challenge to do it better**
- **Outlook**

Nanotechnology is...

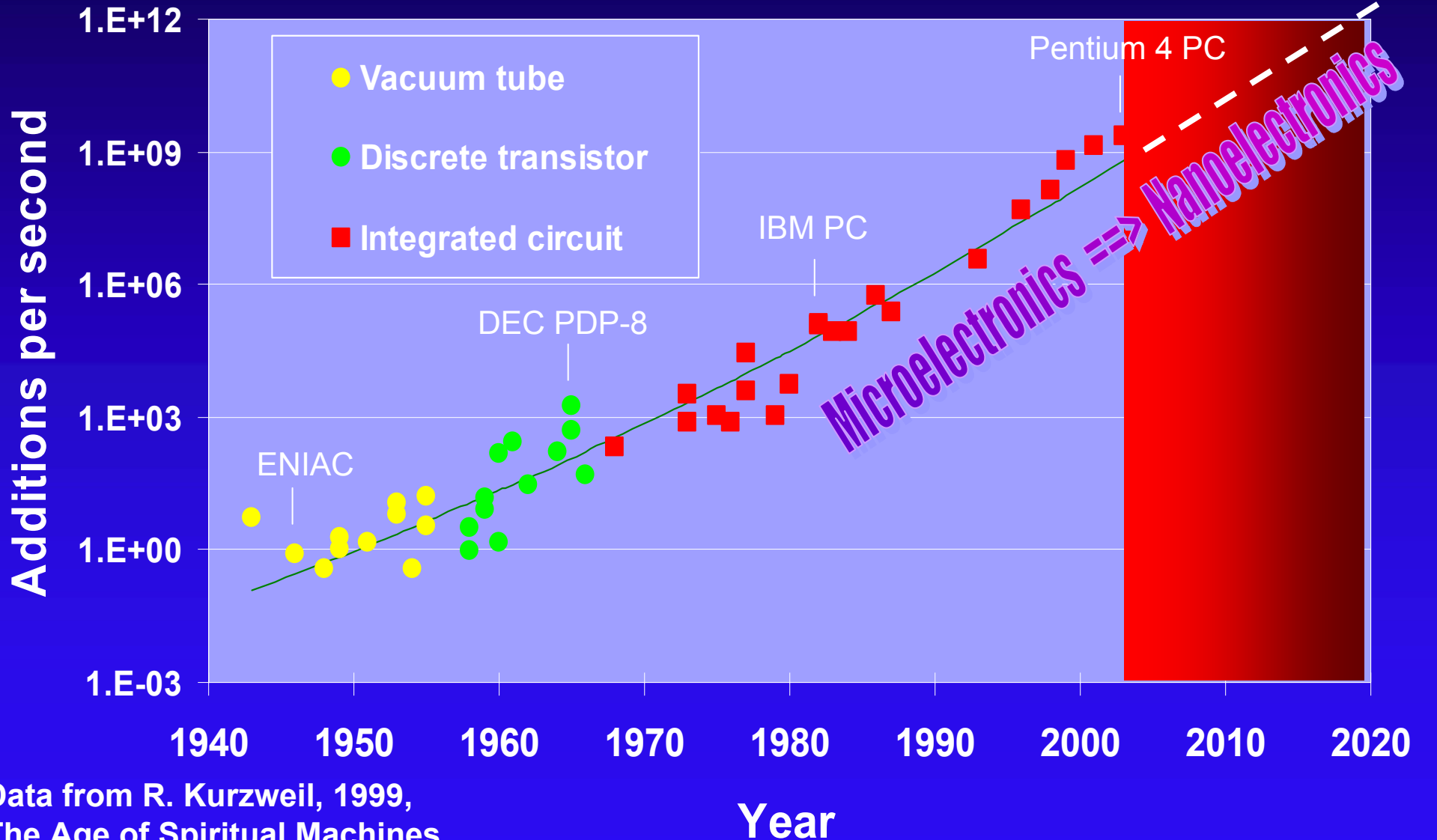
“Research and technology development at the atomic, molecular or macromolecular levels, in the length scale of approximately 1 – 100 nm range...”

National Science Foundation

www.nsf.gov/home/crssprgm/nano/omb_nifty50.htm

By the NSF definition, silicon microelectronics is already a nanotechnology.

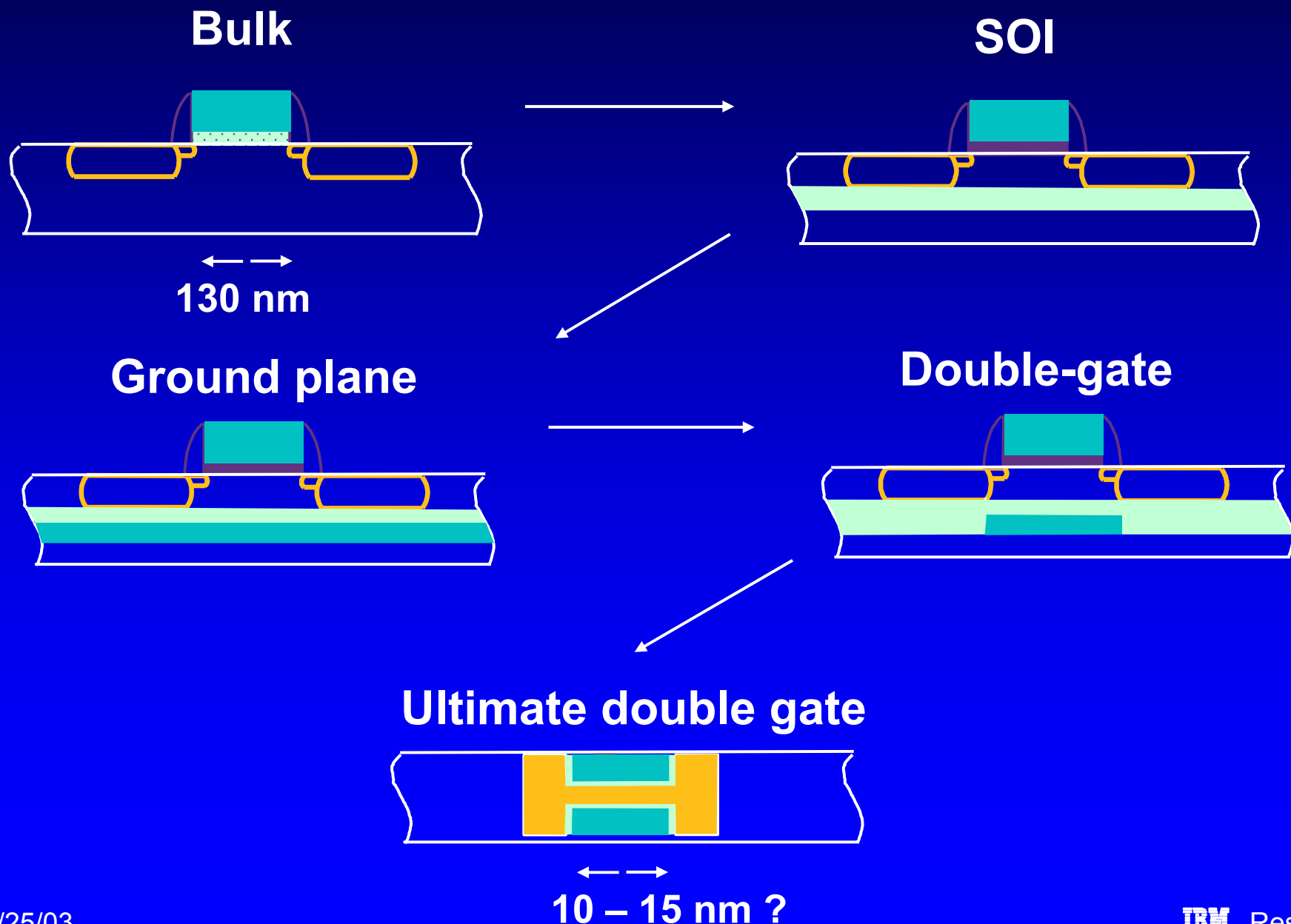
\$1000 buys...



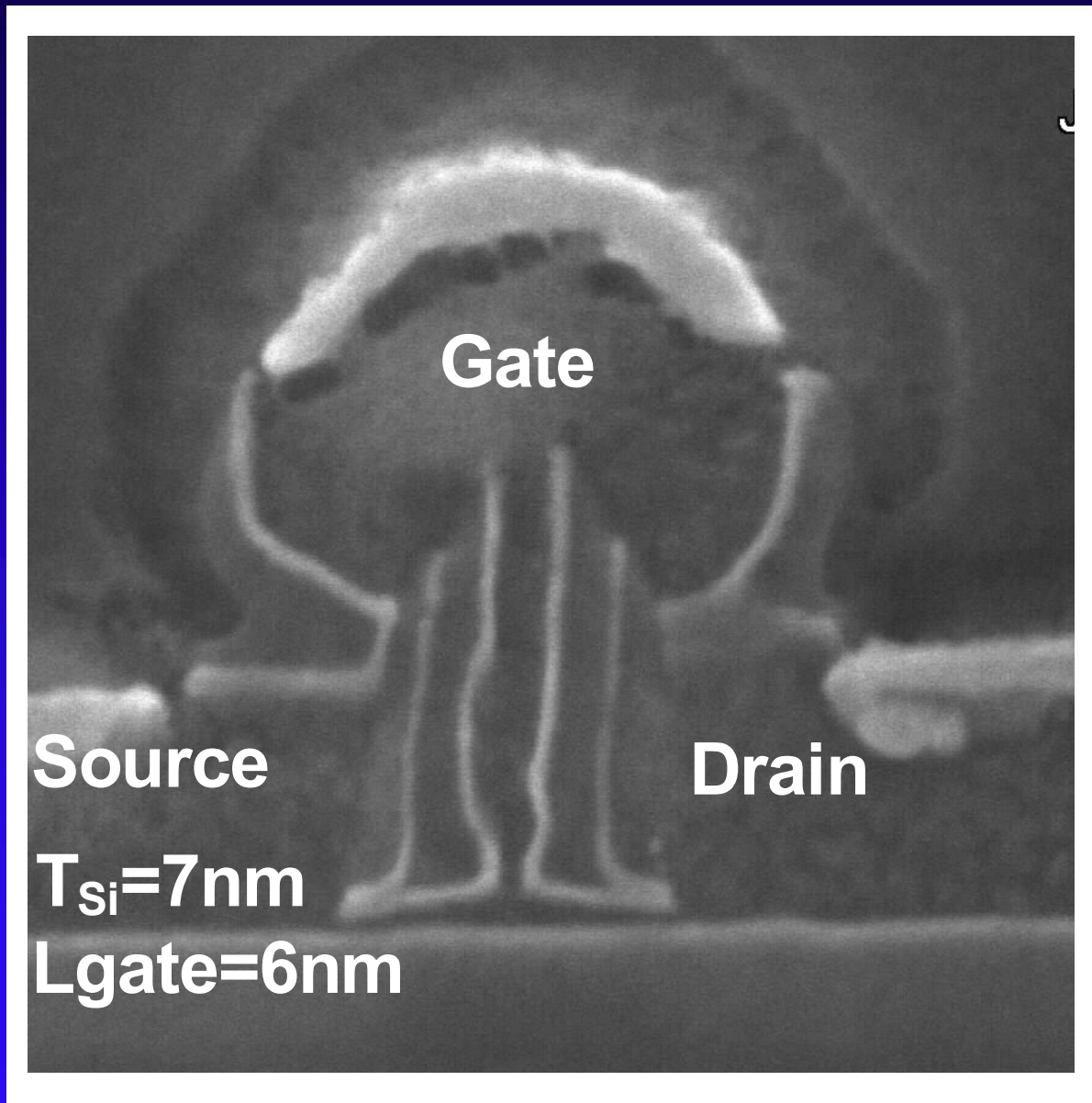
Data from R. Kurzweil, 1999, The Age of Spiritual Machines

T.N. Theis 3/25/03

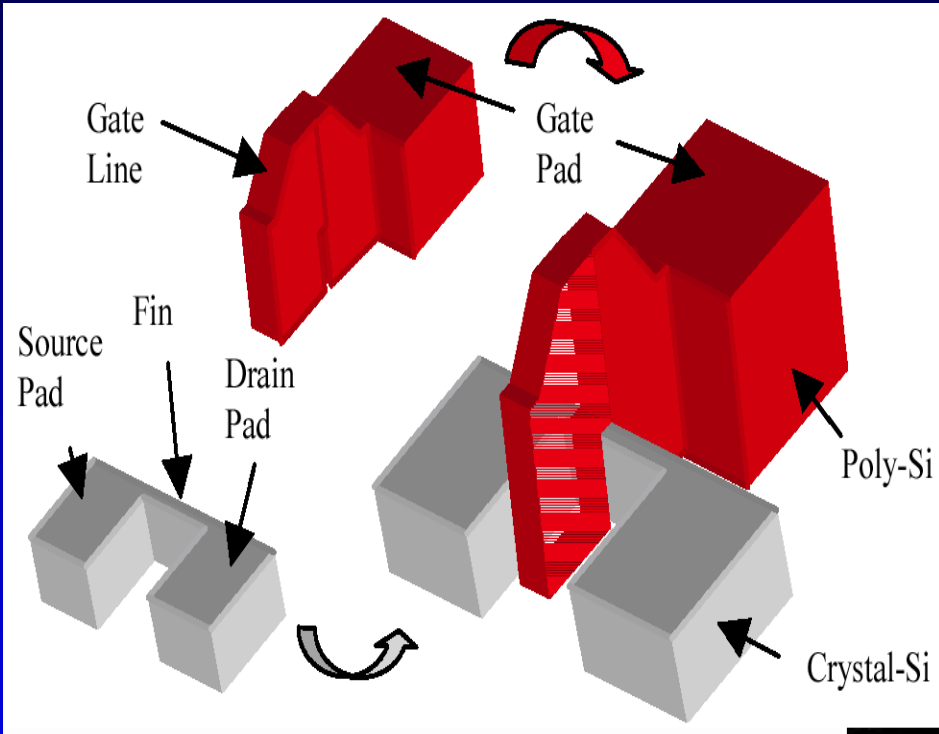
The silicon transistor has become a nanodevice.



An Experimental Silicon Transistor

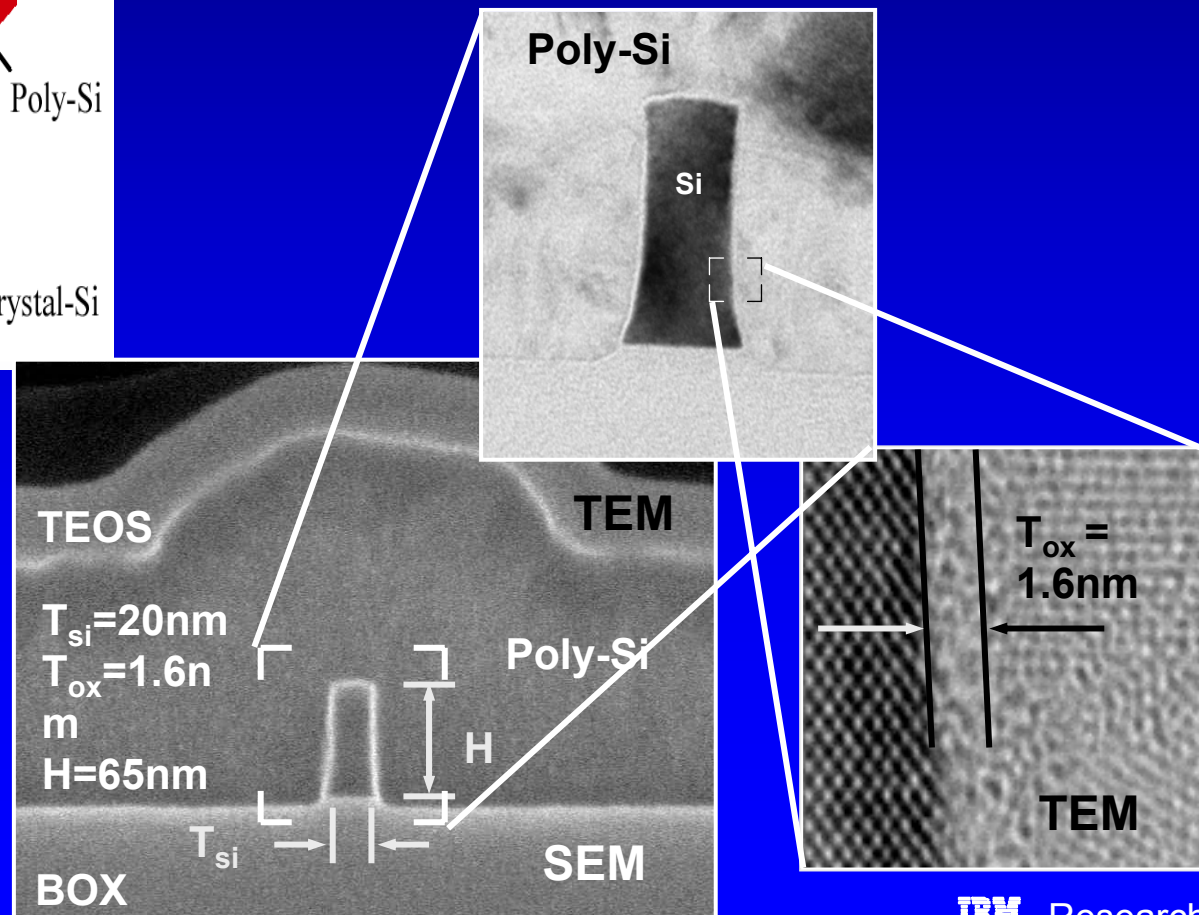


Approaching the ultimate silicon nanodevice (a double-gate Transistor or FinFET)

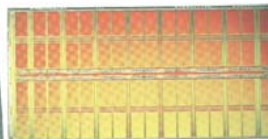
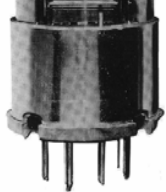
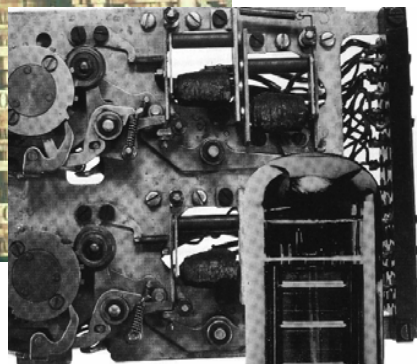
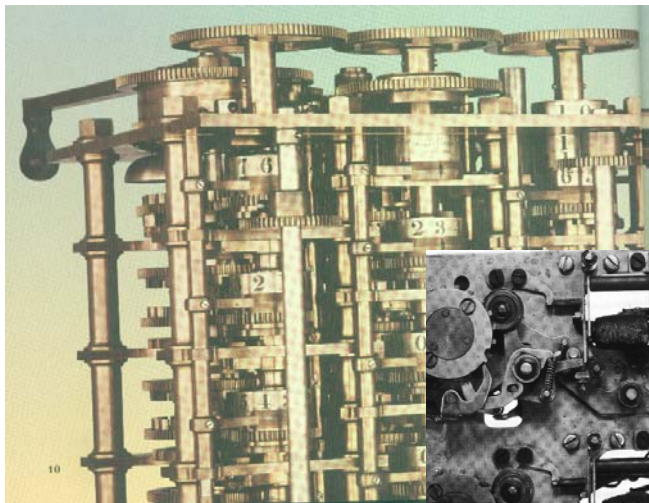


60 nm channel length FET

Cross-section



Is there a successor to silicon?



principle
features

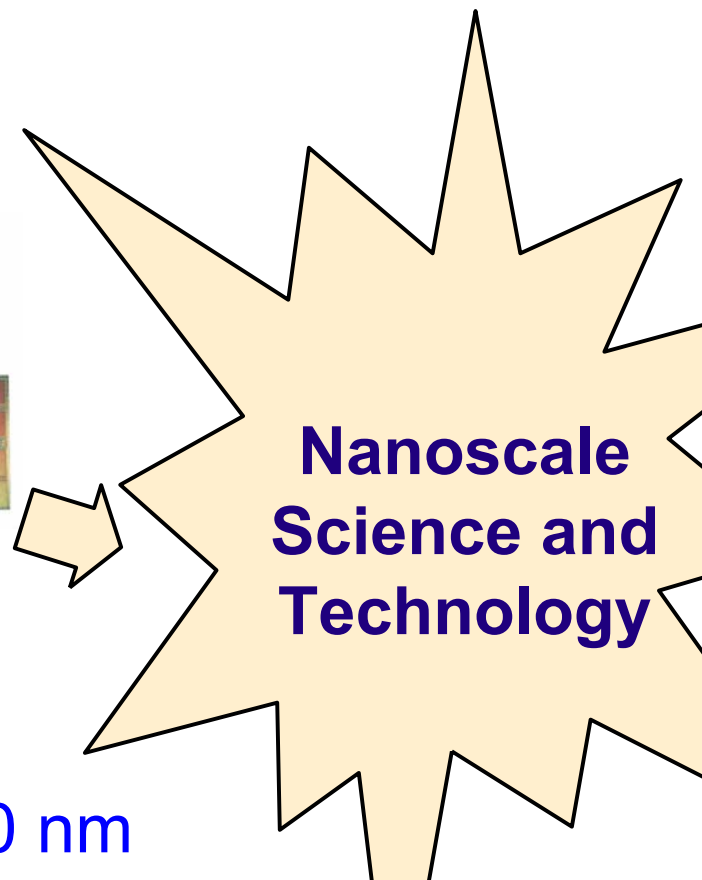
specified to: $\sim 1\text{mm}$



$\sim 10\ \mu\text{m}$

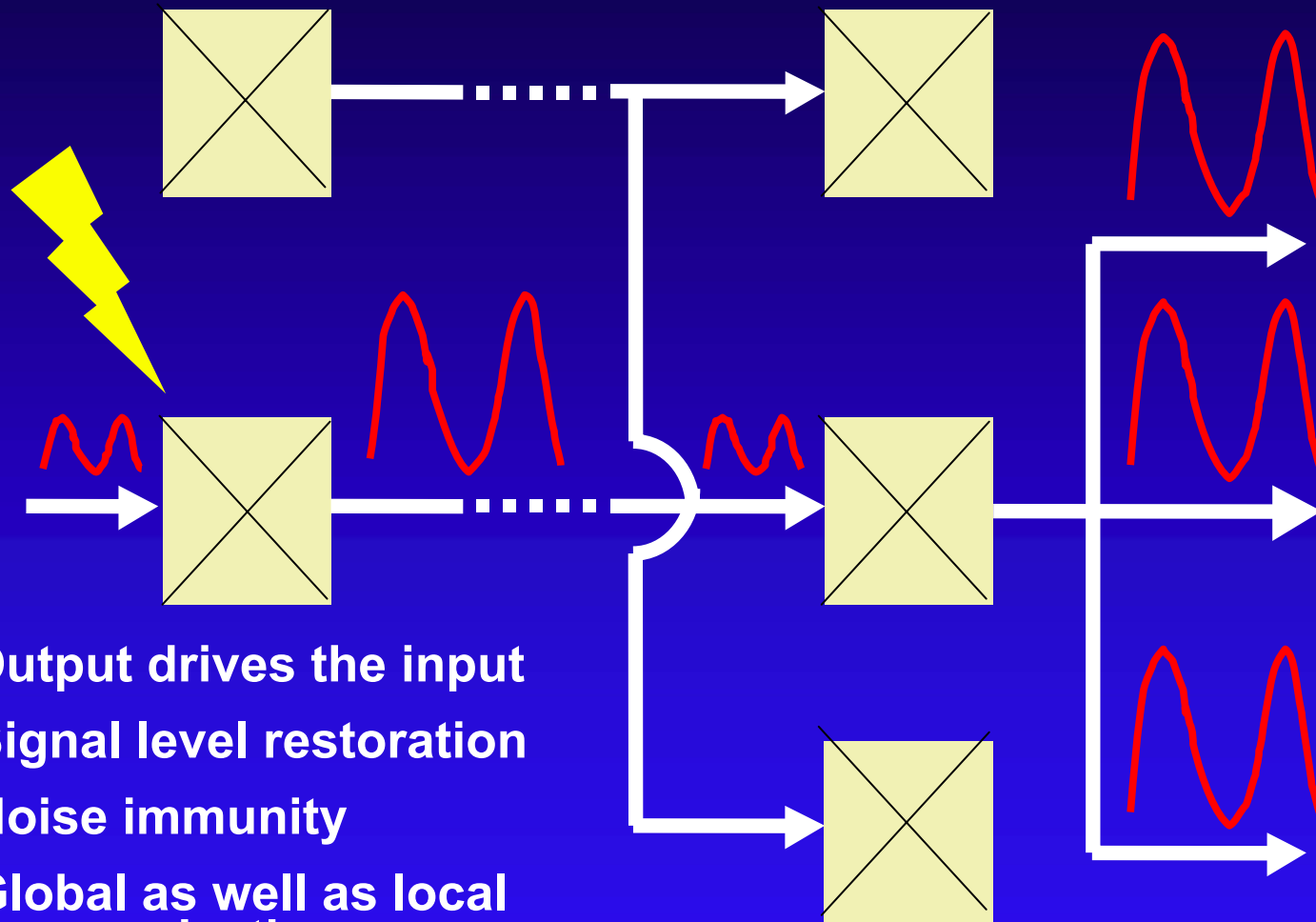


$\sim 100\ \text{nm}$



**Nanoscale
Science and
Technology**

Attributes of Successful Digital Logic Devices

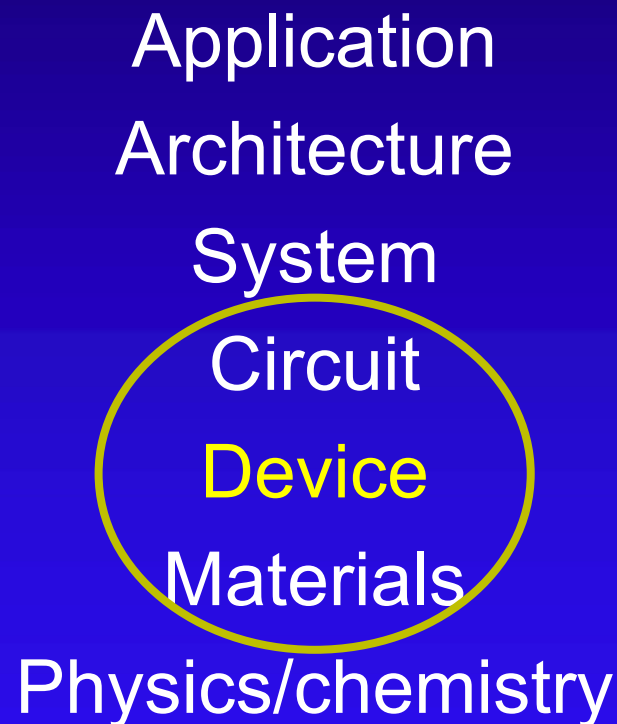


- Output drives the input
- Signal level restoration
- Noise immunity
- Global as well as local communications

After H.-S. P. Wong, "Novel Device Options" in Sub-100nm CMOS Short Course, *IEDM*, 1999

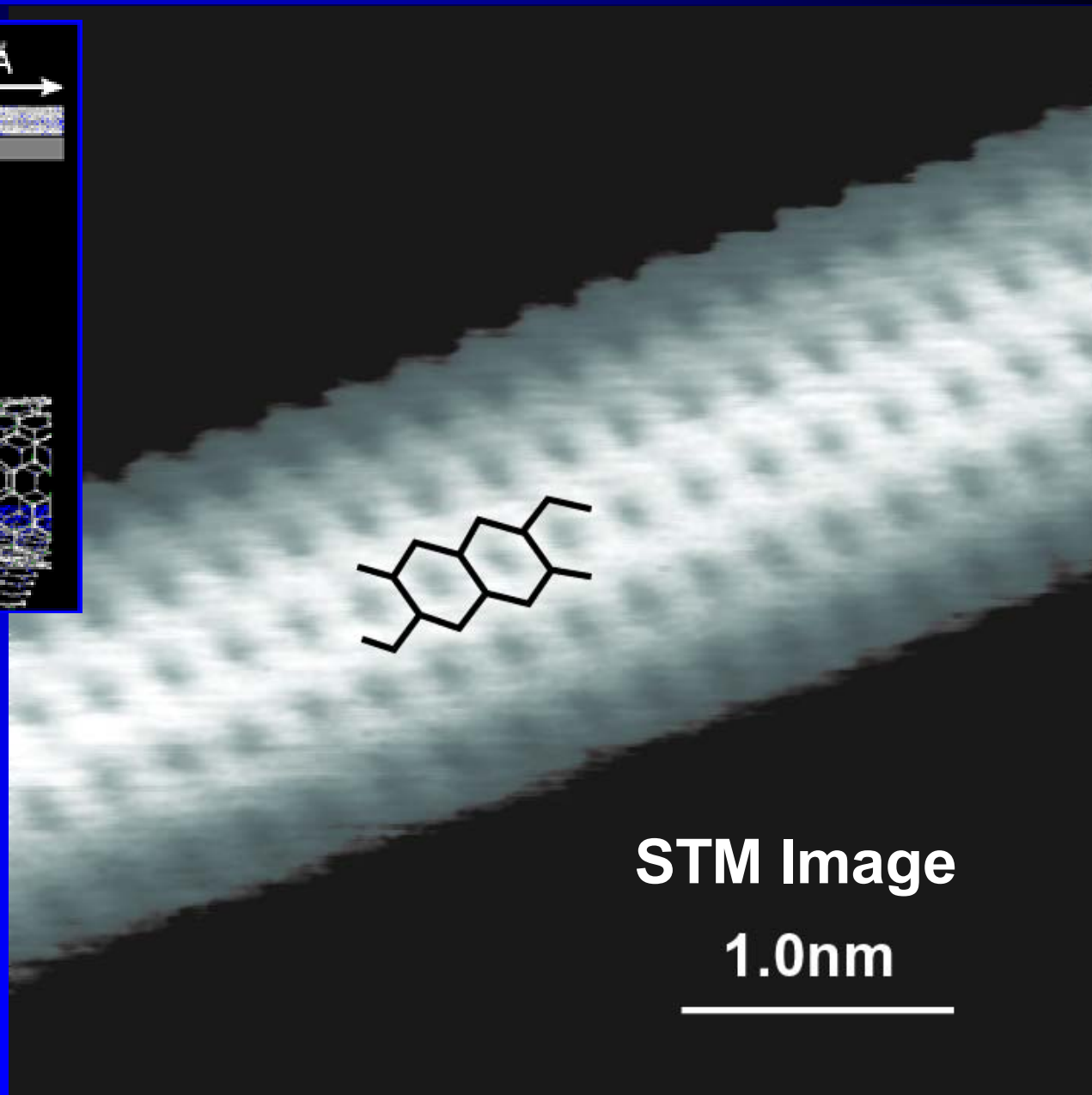
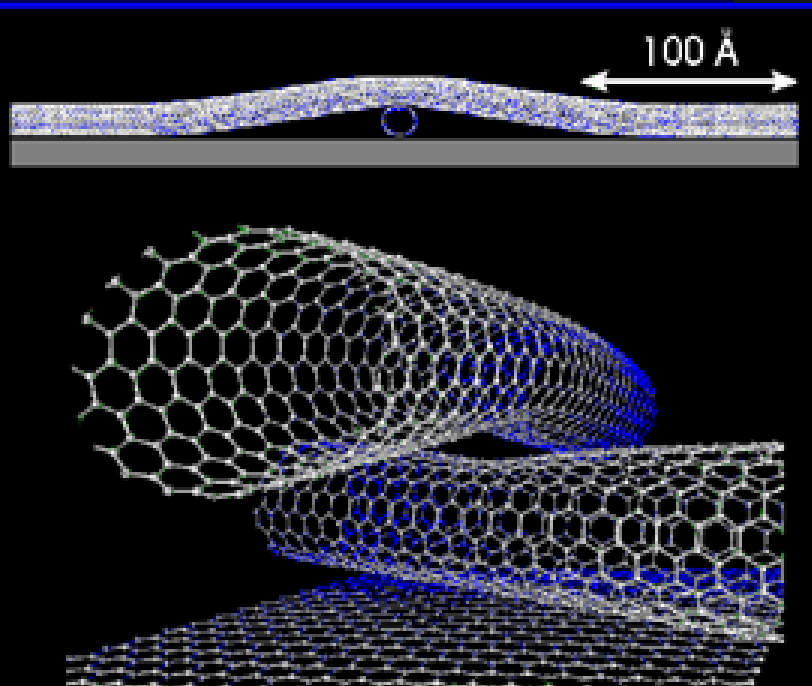
“Revolutionizing” a large, complex, stratified industry is not easy.

- Sphere of successful influence: +/- one layer

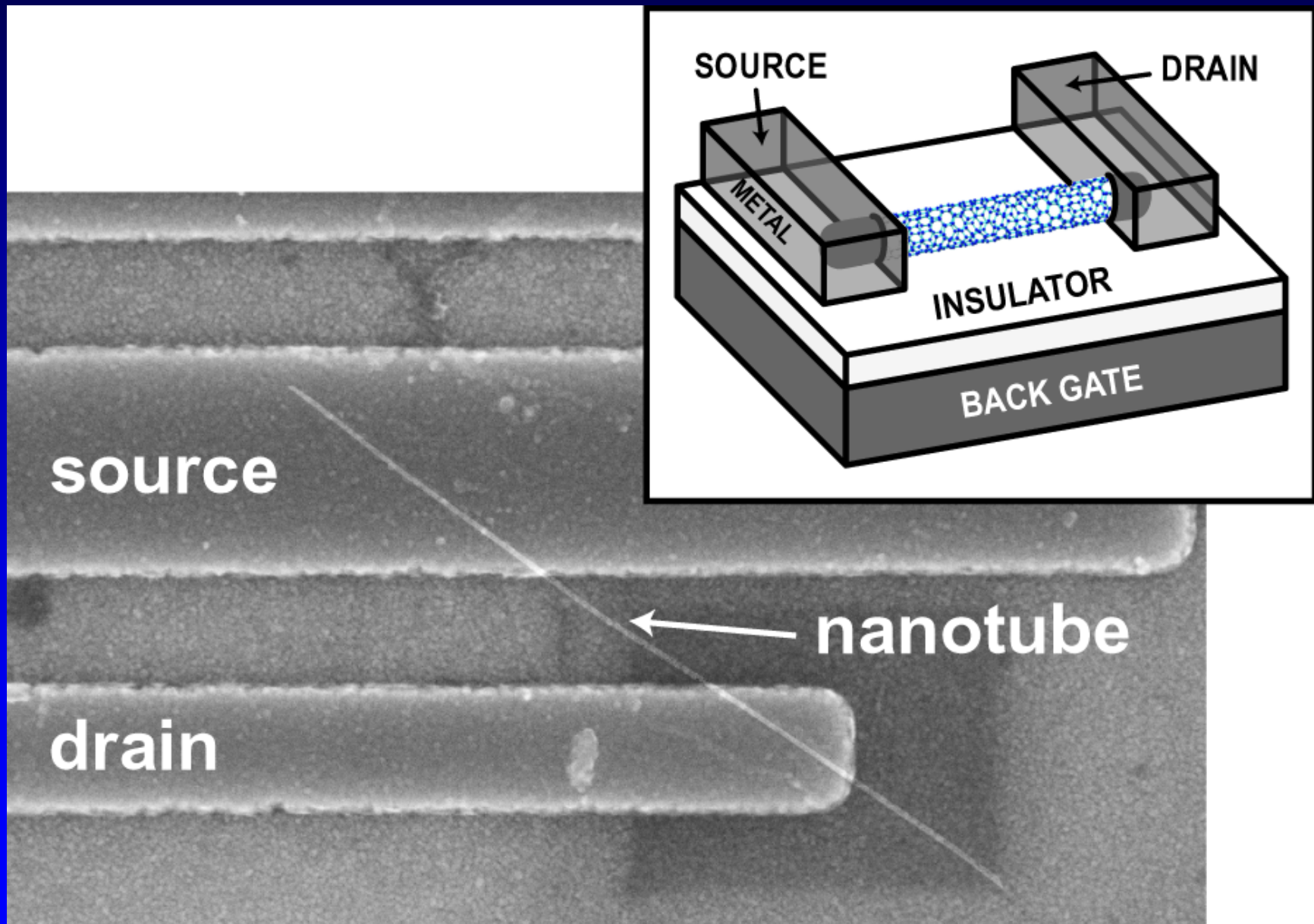


Adapted from M. Horowitz, in *Focus Center Research Program (MARCO) MSD-C2S2 Topical Workshop*, Nov. 12, 2001

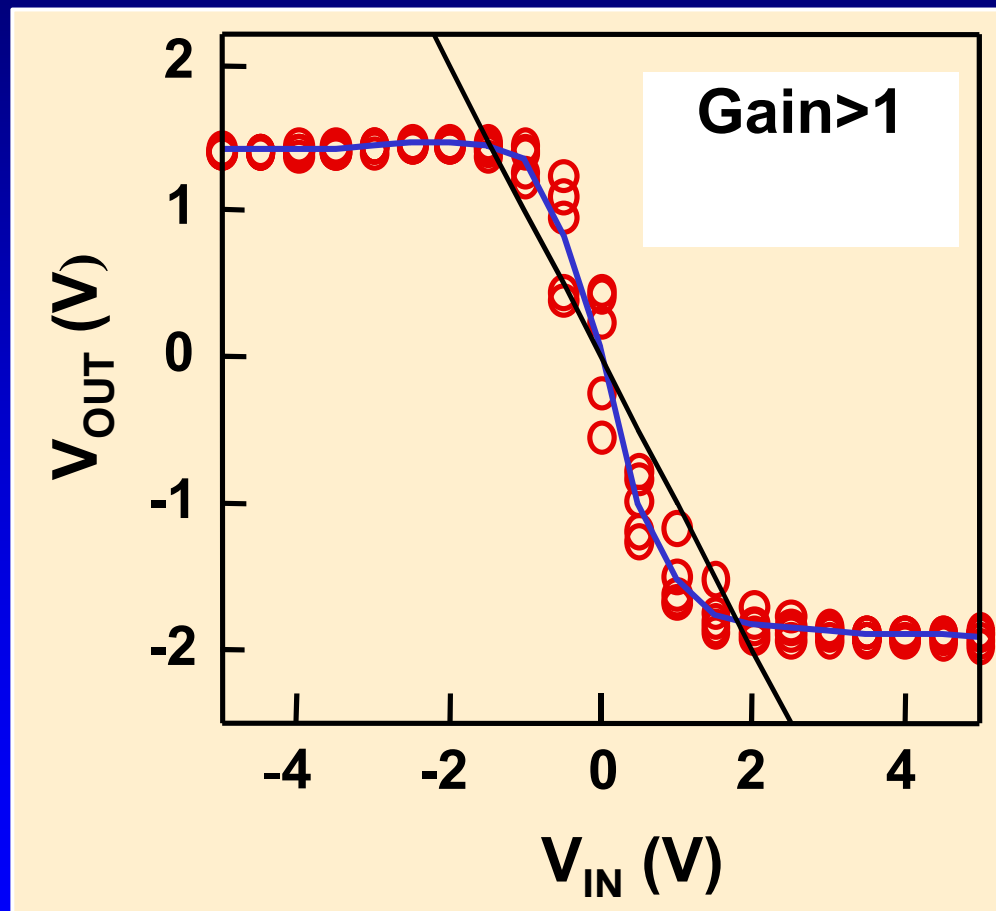
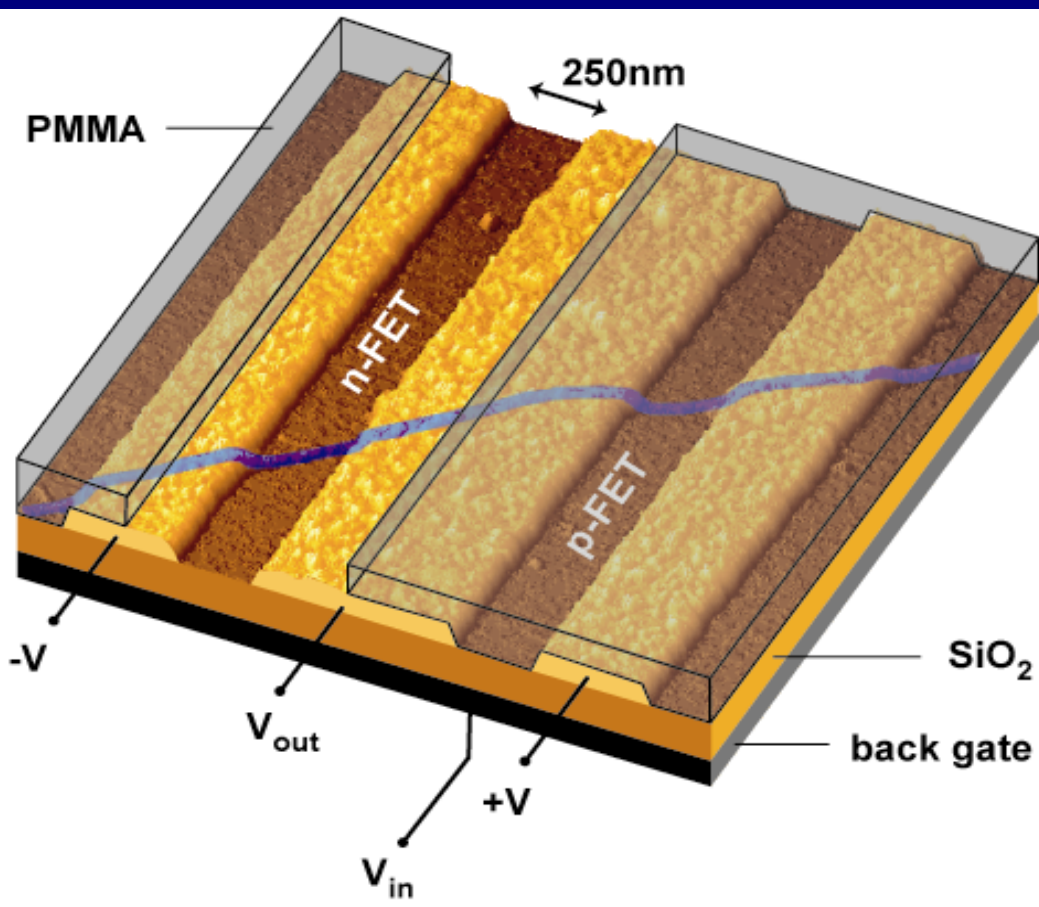
Carbon Nanotubes



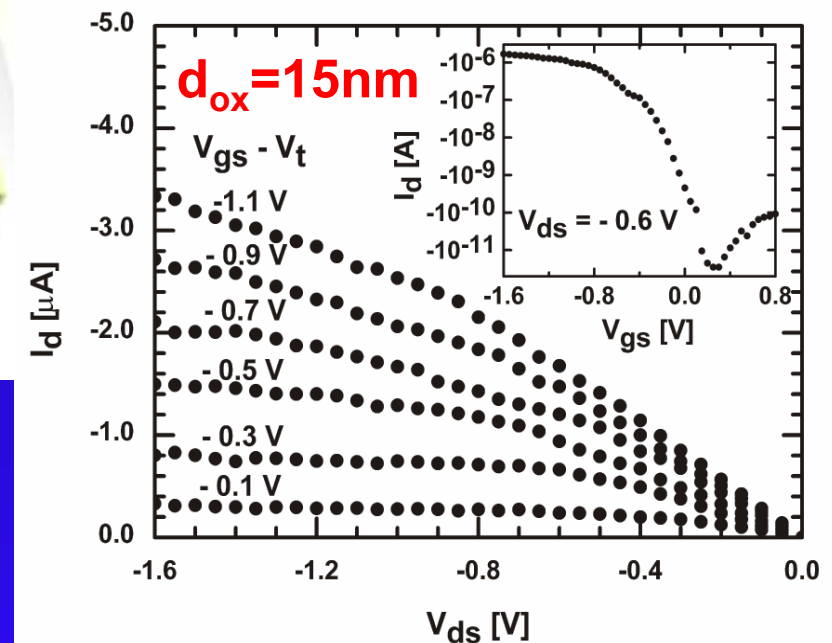
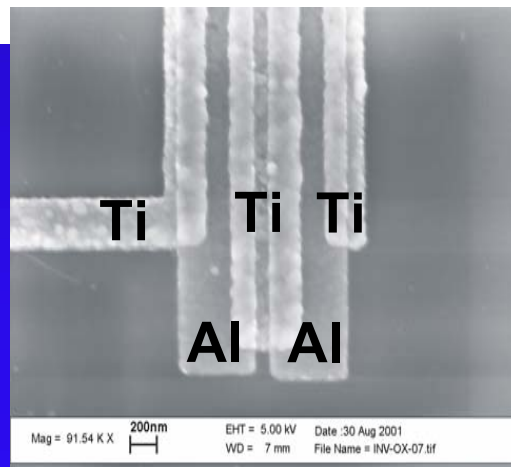
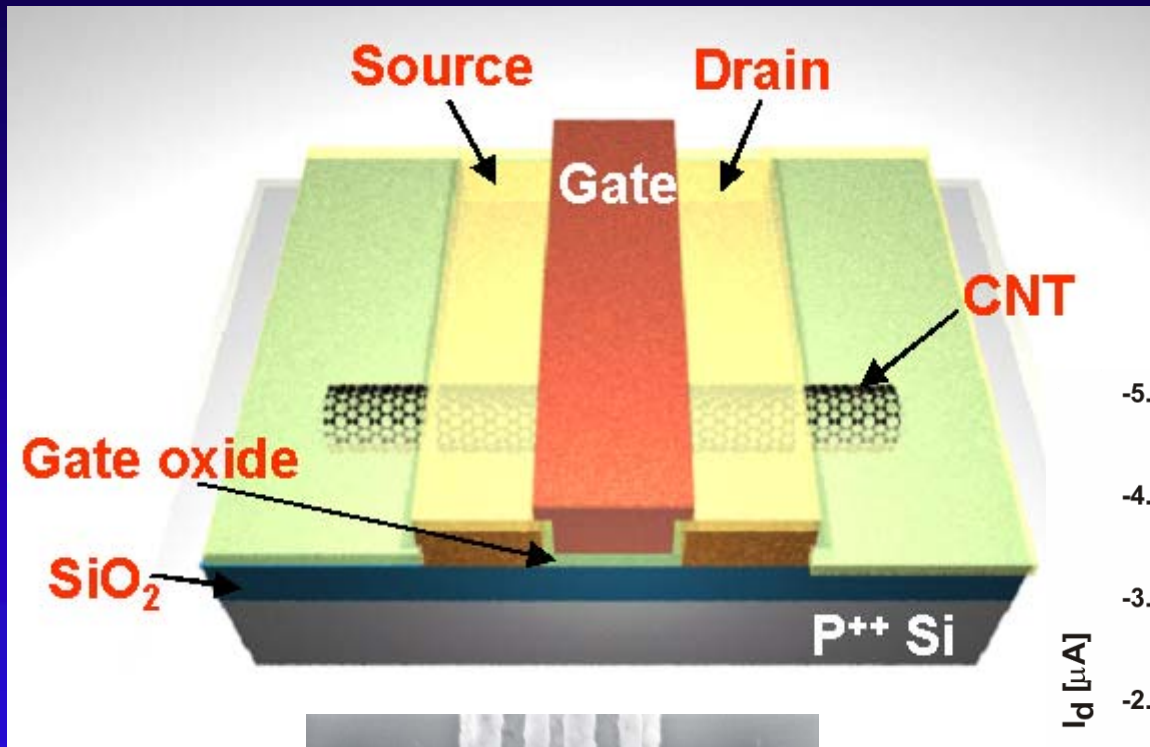
An alternative logic switch -- A simple Carbon Nanotube Transistor



Carbon nanotube intra-molecular logic gate (NOT gate, voltage inverter)



Top-gate carbon nanotube transistor



Appl. Phys. Lett. 80, 3817 (2002)

Comparison with silicon

| | p-MOSFET ^{a)} | p-CNFET |
|---------------------------------------|------------------------|-------------|
| channel length | 50nm | 260nm |
| gate oxide thickness | 1.5nm | ~15nm |
| transconductance | 650mS/mm | 2300mS/mm |
| drive current ($V_g - V_t = -1.0V$) | 650mA/mm | 2100mA/mm |
| threshold voltage | -0.2V | -0.5V |
| I_{On}/I_{Off} | $10^6 - 10^7$ | $\sim 10^6$ |
| subthreshold slope | 70mV/dec | 130mV/dec |

^{a)} R. Chau et al. Proceedings of IEDM 2001, p.621

Carbon nanotube transistors have promise

because:

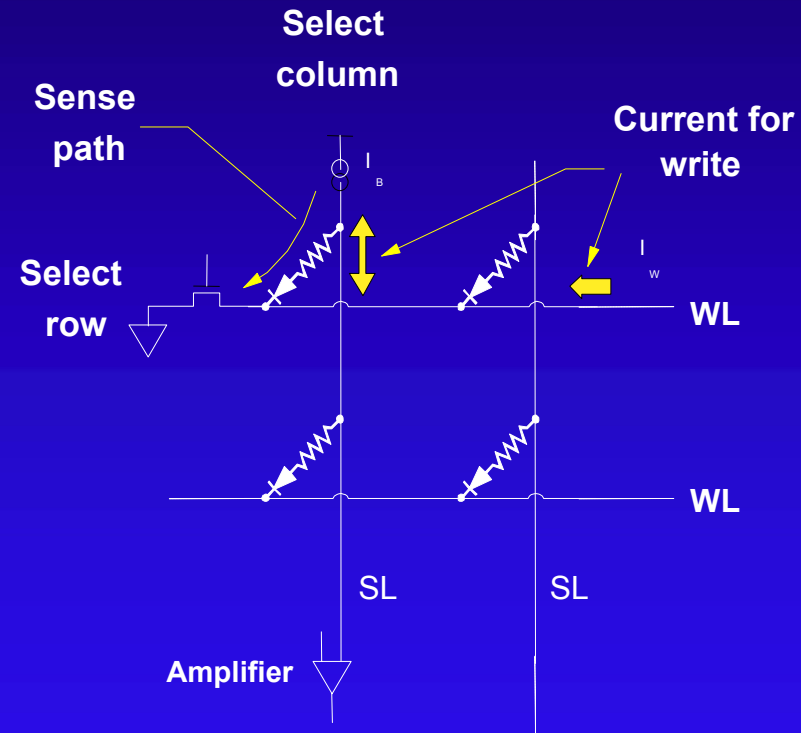
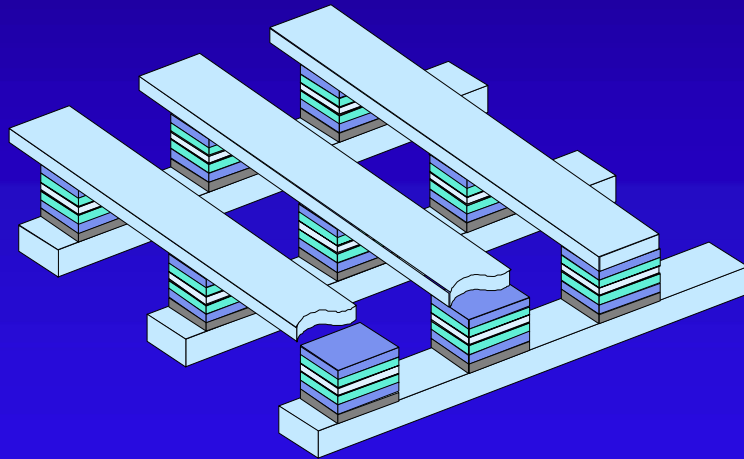
- Carrier transport is ballistic and ambipolar
- All bonds are satisfied, stable, and covalent
- Chemical synthesis controls a key dimension
- Device is not “wed” to a particular substrate

but much remains to be done:

- Scalability
- Contacts
- Doping
- Device stability (charge trapping)
- High yield, selective growth of nanotubes
(control of the diameter, length, chirality, position)

Memory

Everyone wants non-volatile, low-power memory.
Everyone wants a dense cross-point memory.



There is no conceptual problem with bistable hysteretic two-terminal devices as cross-point memory cells.

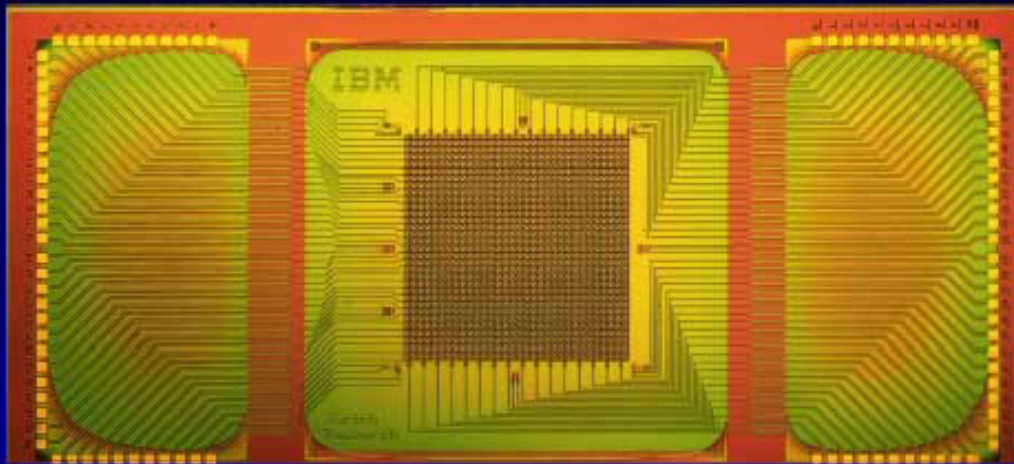
Memory Landscape

| | volatile | non-volatile |
|---------------------|----------|--|
| 1Transistor | 1T-DRAM | <ul style="list-style-type: none"> ■ Floating-gate ■ SONOS ■ SET |
| Multiple Transistor | SRAM | |
| 1T-1C | DRAM | FeRAM |
| 1T-1R | | <ul style="list-style-type: none"> ■ MRAM ■ polymer RAM ■ molecular memory ■ phase-change RAM ■ perovskite MIM RAM |
| 1R (Cross-point) | | <ul style="list-style-type: none"> ■ MRAM ■ polymer RAM ■ molecular memory ■ perovskite MIM RAM |

Memory (continued)

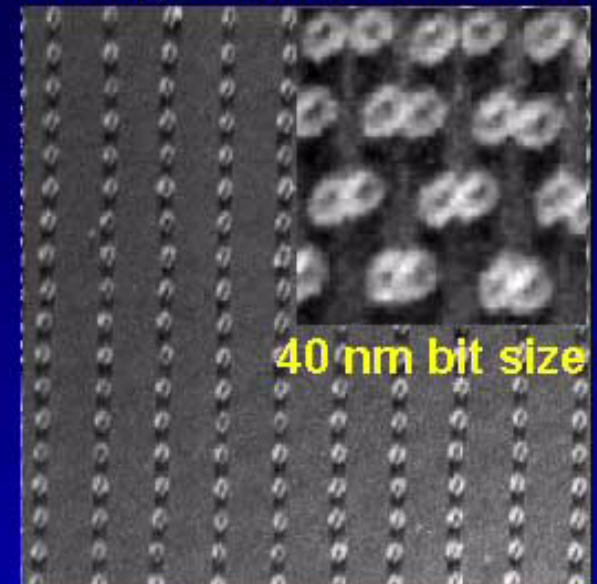
- **There is no shortage of two-terminal, bistable hysteretic memory devices and materials!**
 - **MTJ MRAM** (IBM/Infineon, Motorola, Toshiba, NEC, Sony, HP, Honeywell, Micromem, Motorola, NVE, Samsung, USTC, Toshiba)
 - **Chalcogenide glasses** (Intel/Ovonyx, Micron Technology/Axon Technologies, Samsung, ST Micro)
 - **Polymeric resistive memory** (Intel/Opticom, AMD/Coatue)
 - **Molecular memories** (Hewlett Packard, Molecular Electronics Corp., Zettacore, Nantero, ...)
- **But ...**
 - **All** memories require logic devices for read/write. Candidate memory cells must be integrated with logic.
 - Replacing a transistor-based memory cell with a cross-point cell will typically reduce performance.

Millipede: A nanomechanical approach to storing information

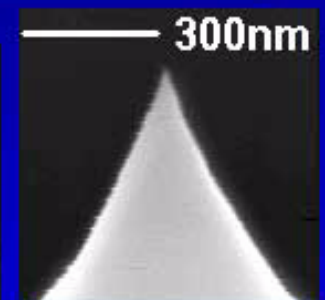
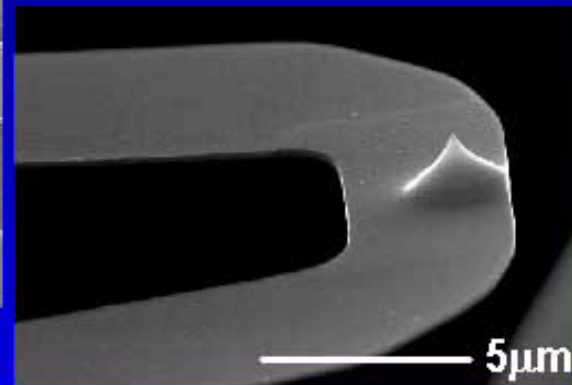
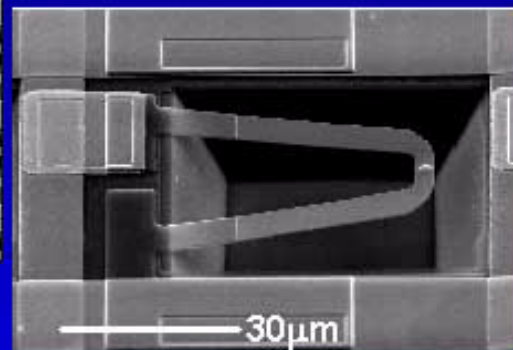
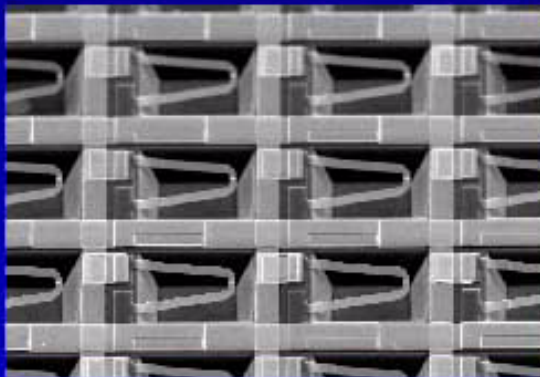


32 x 32 (1024) Cantilever Array

Thermomechanical writing in polymer media

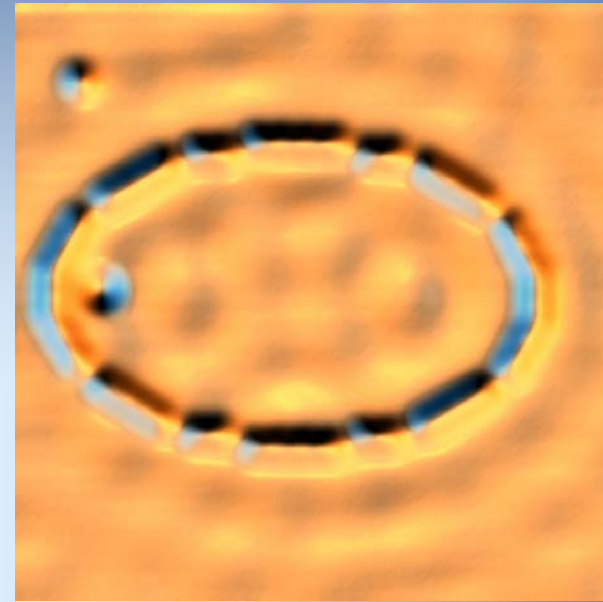
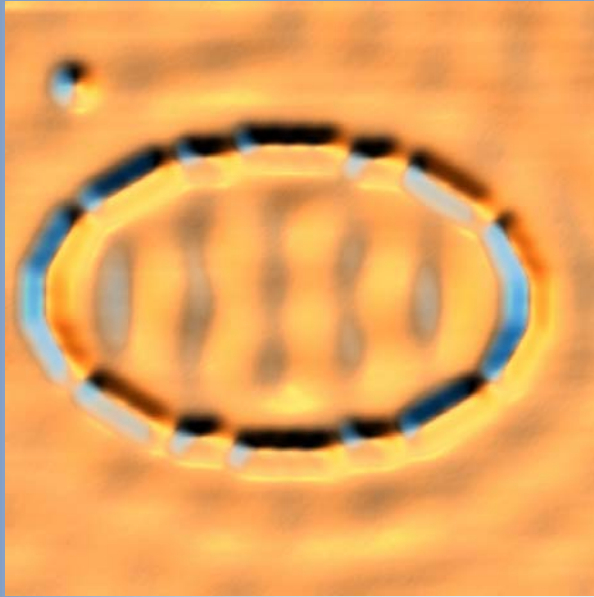


40 nm bit size

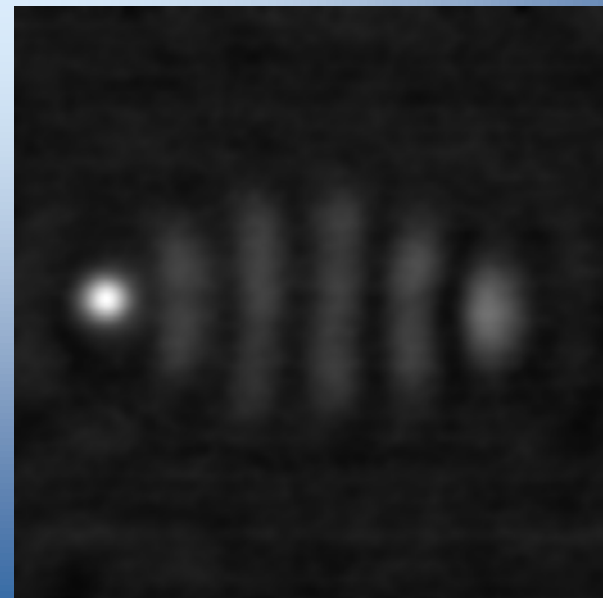


The Quantum Mirage: Single Channel Information Transport

Topograph

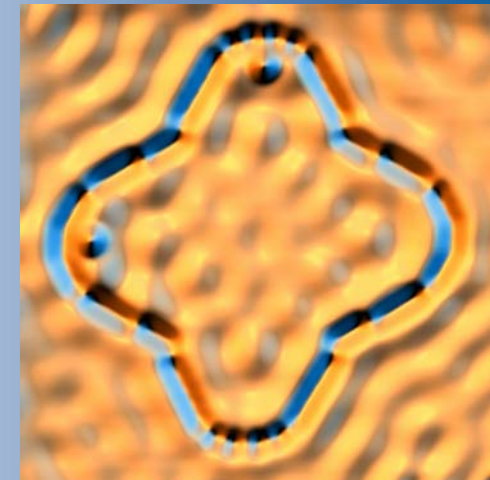
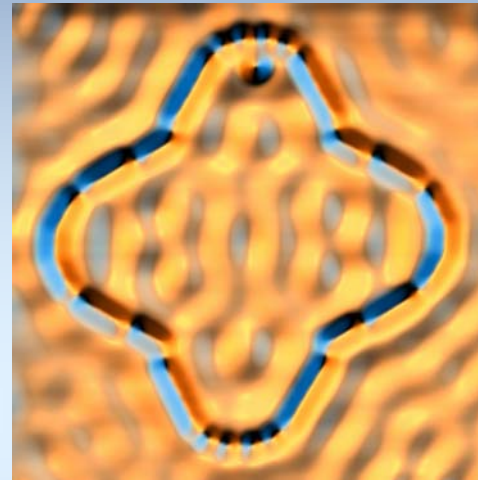
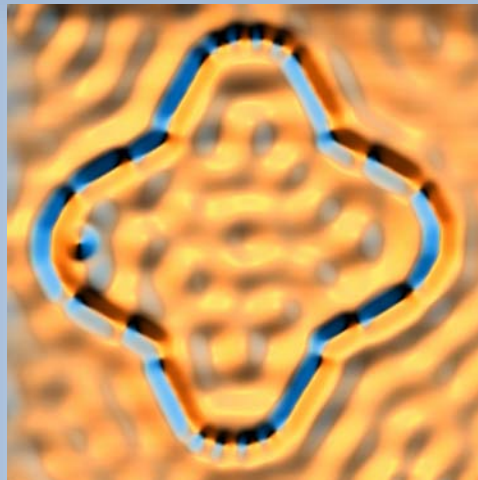
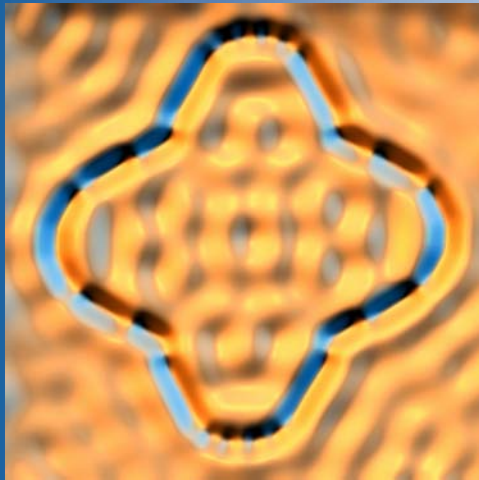


dI/dV difference

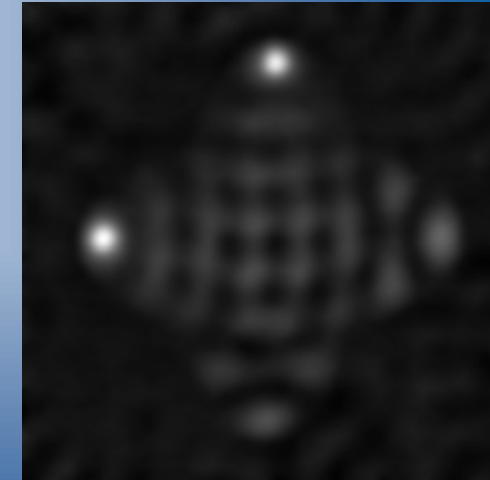
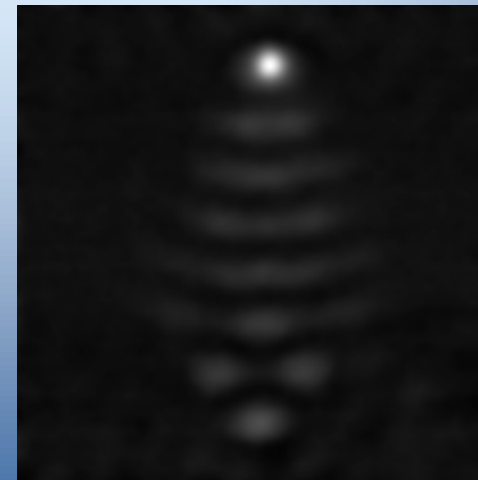
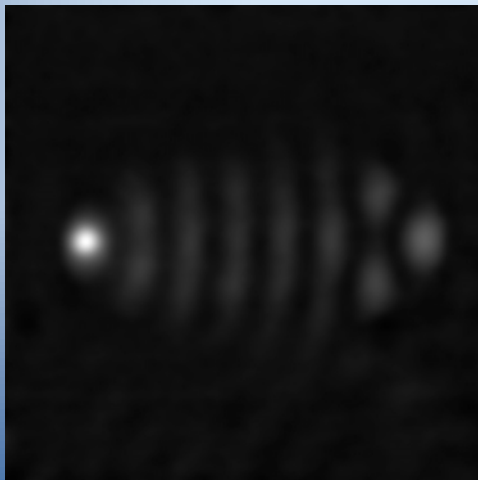
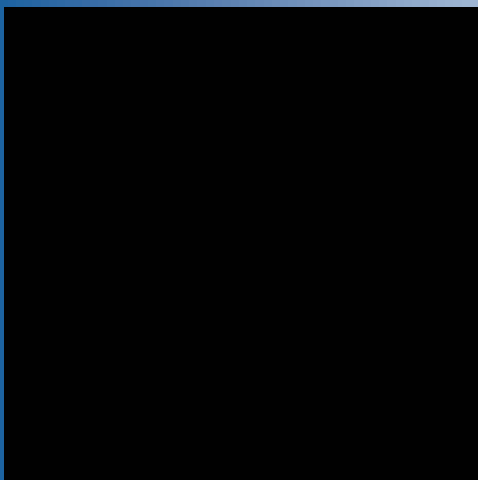


Multi Channel Information Transport

Topograph



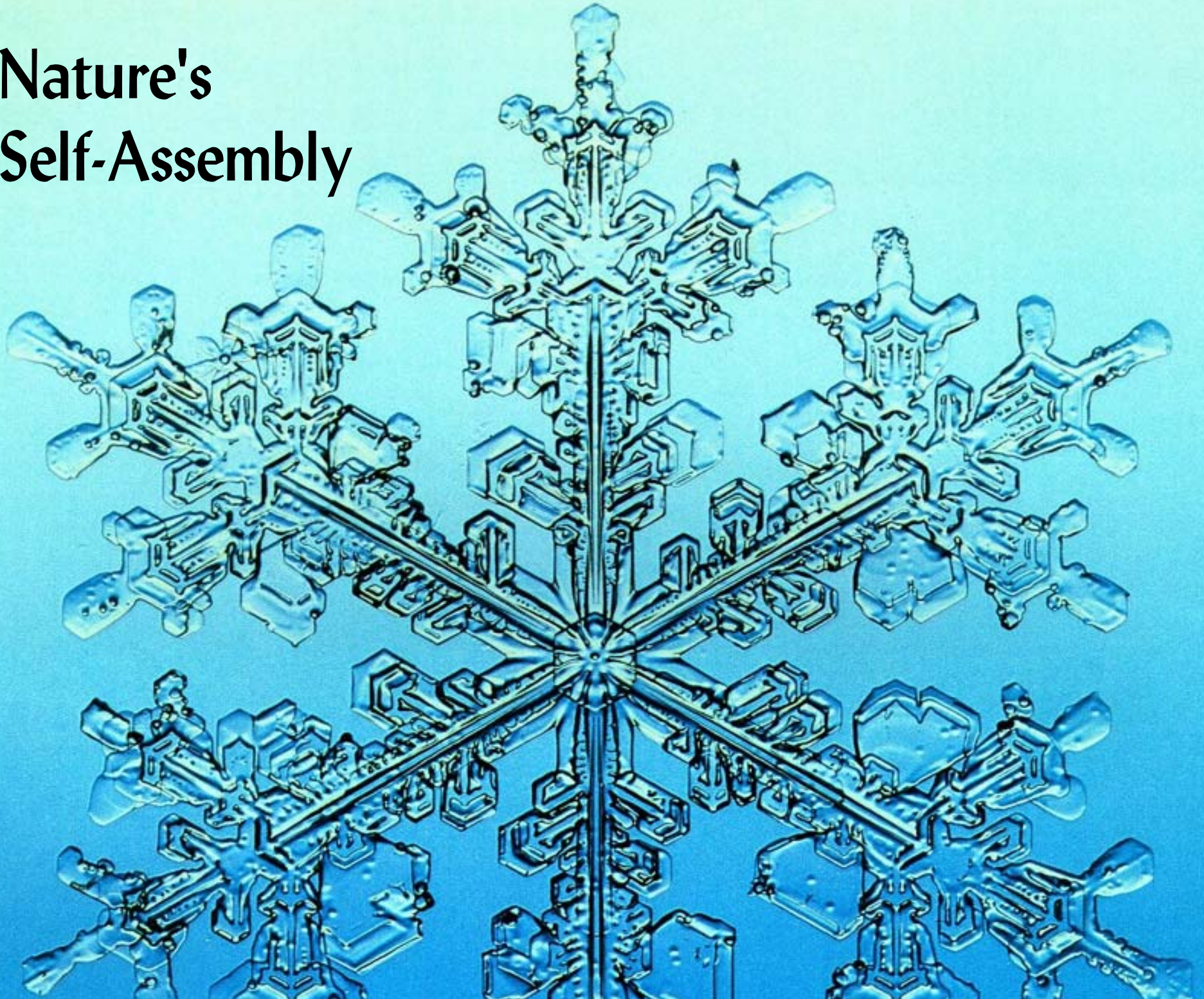
dI/dV difference



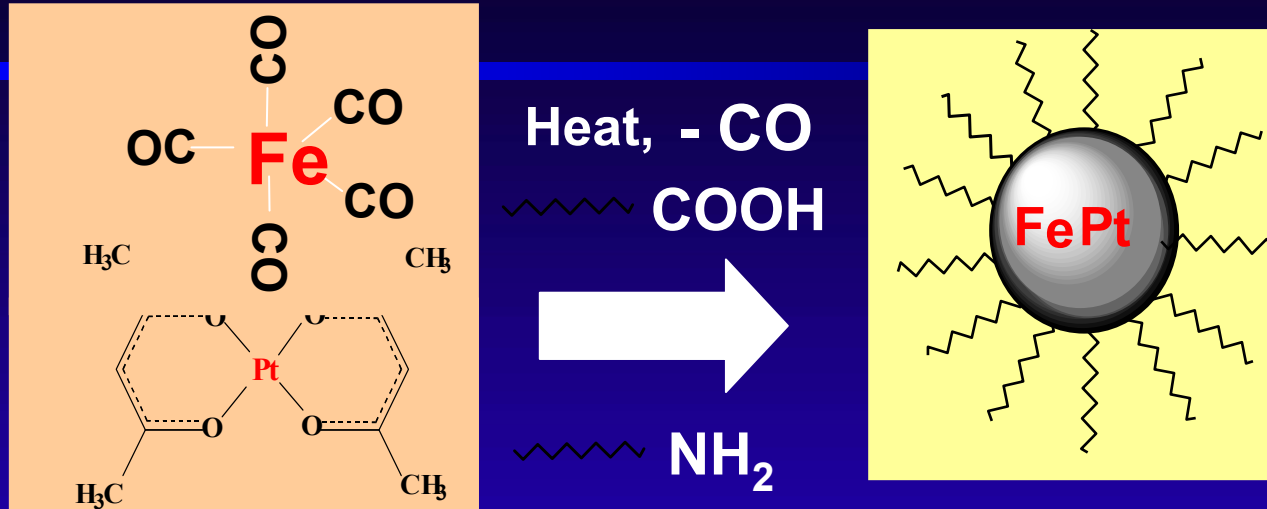
But how can we position atoms cheaply?

**Persuade them to
assemble themselves!**

Nature's Self-Assembly

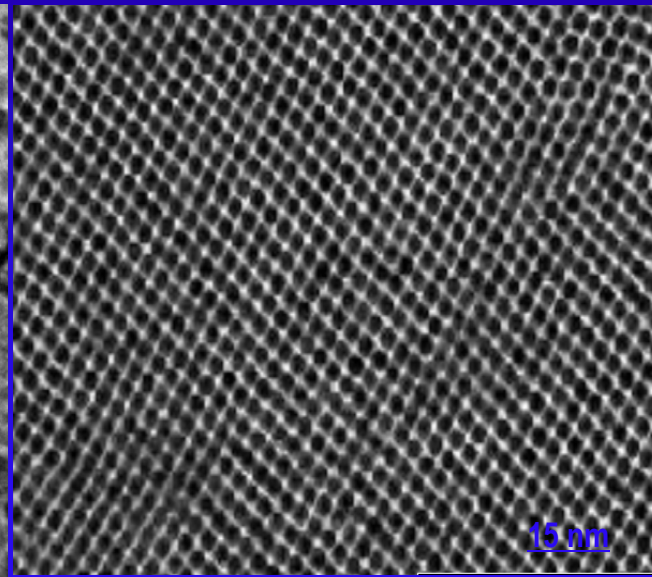
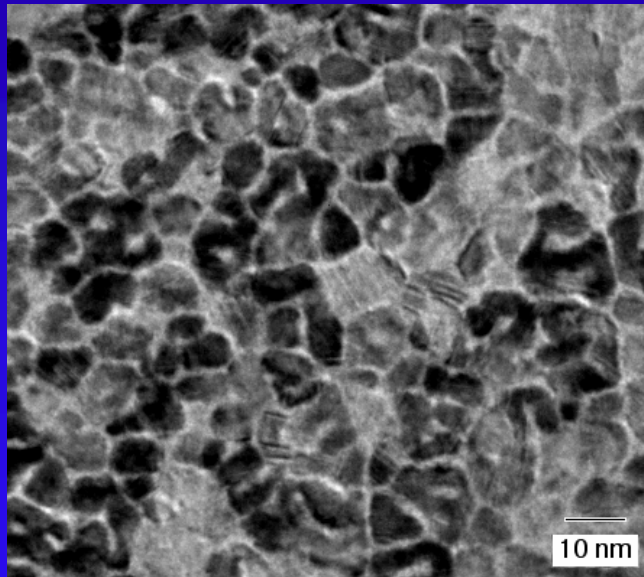


Self-assembled Magnetic Nanocrystals



35 Gbit/in² media

FePt Nanoparticle Arrays

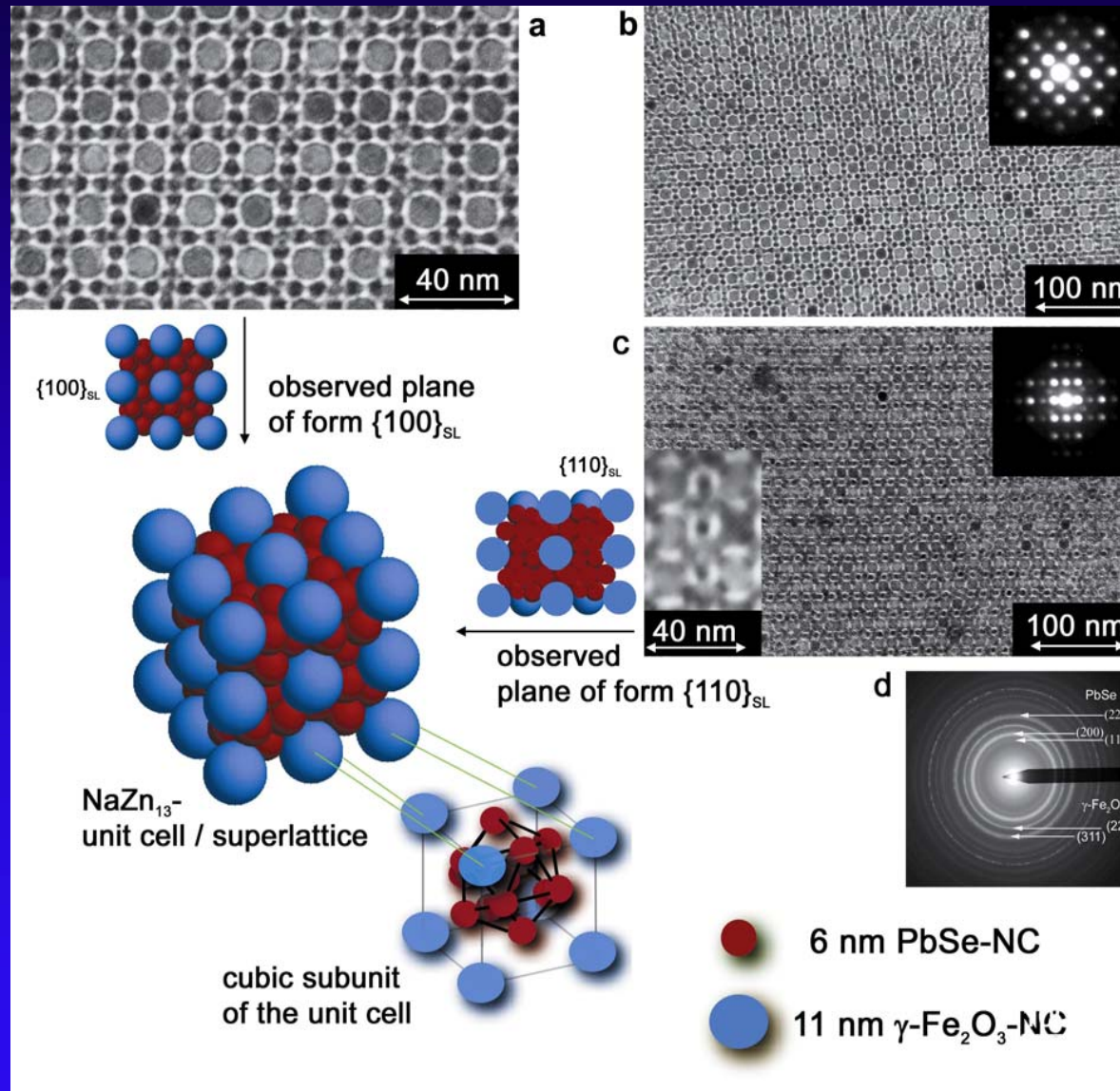


8.5nm grains $\sigma_{\text{area}} \cong 0.5$

4 nm FePt NPs $\sigma_{\text{area}} \cong 0.05$

S. Sun, C. B. Murray, D. Weller, L. Folks, A. Moser, Science, 287, 1989 2000

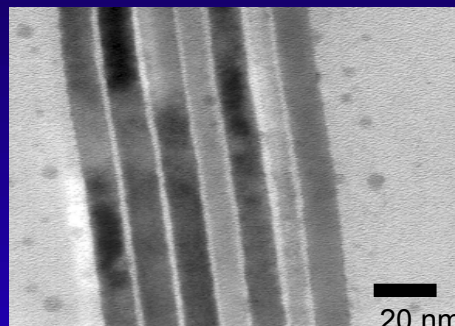
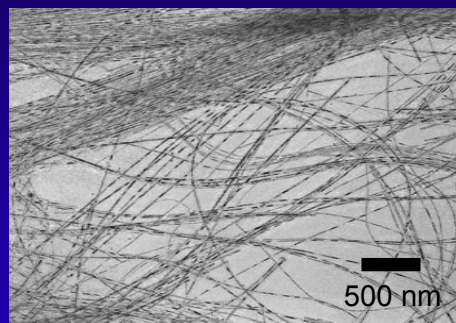
Multi-Component Nanocrystal Superlattices



AB₁₃ binary Nanocrystal Superlattice of PbSe and Fe₂O₃

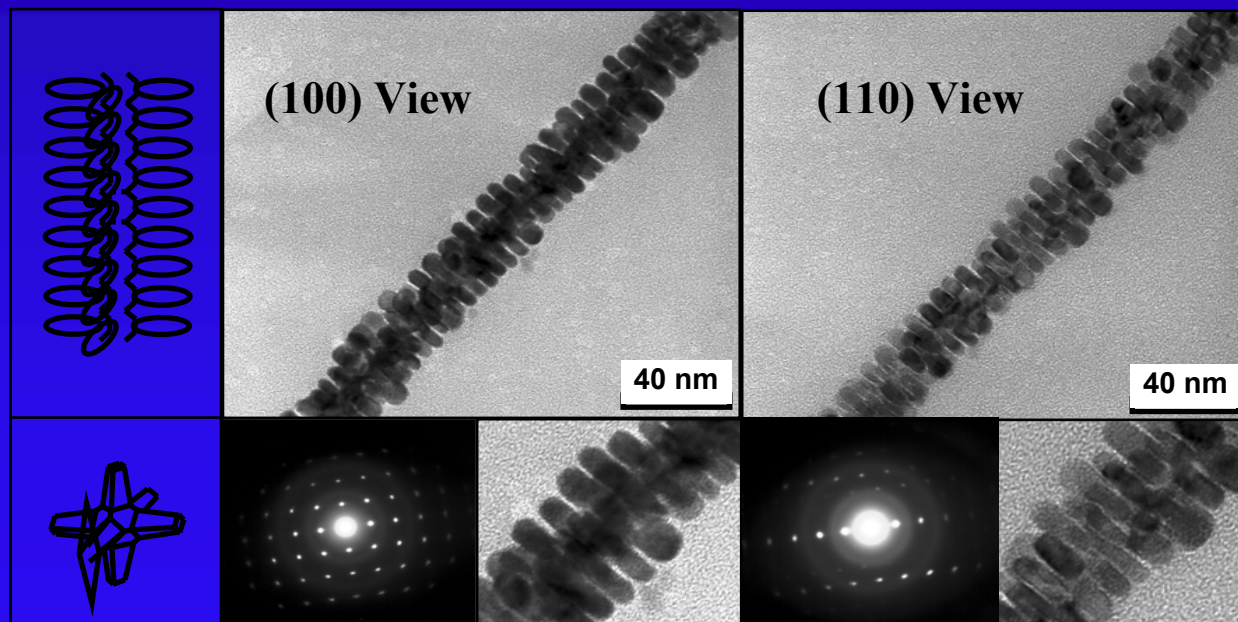
F. X. Redl, K. S. Cho and C. B. Murray.

Semiconductor Nanowires

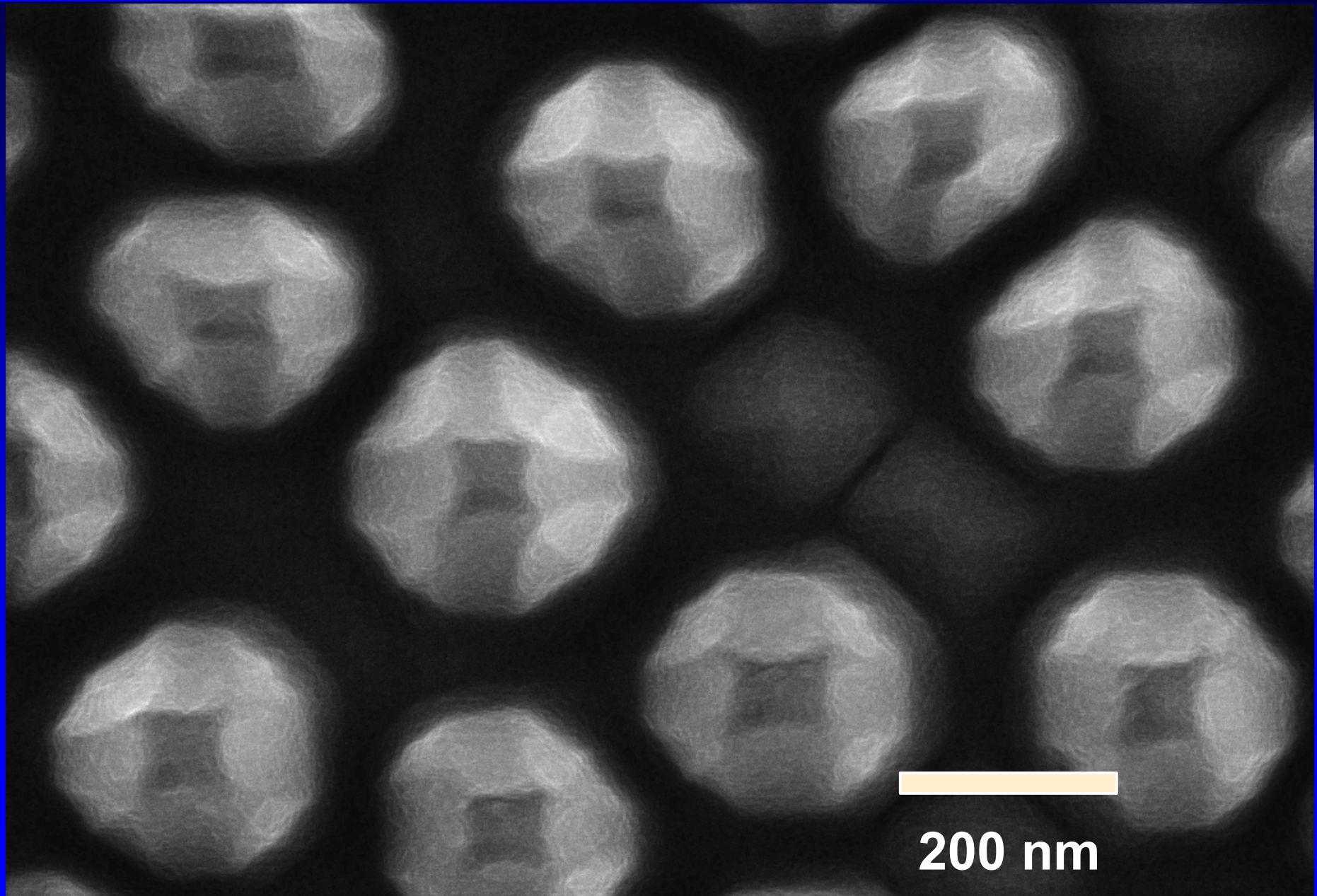


Straight PbSe Nanowires

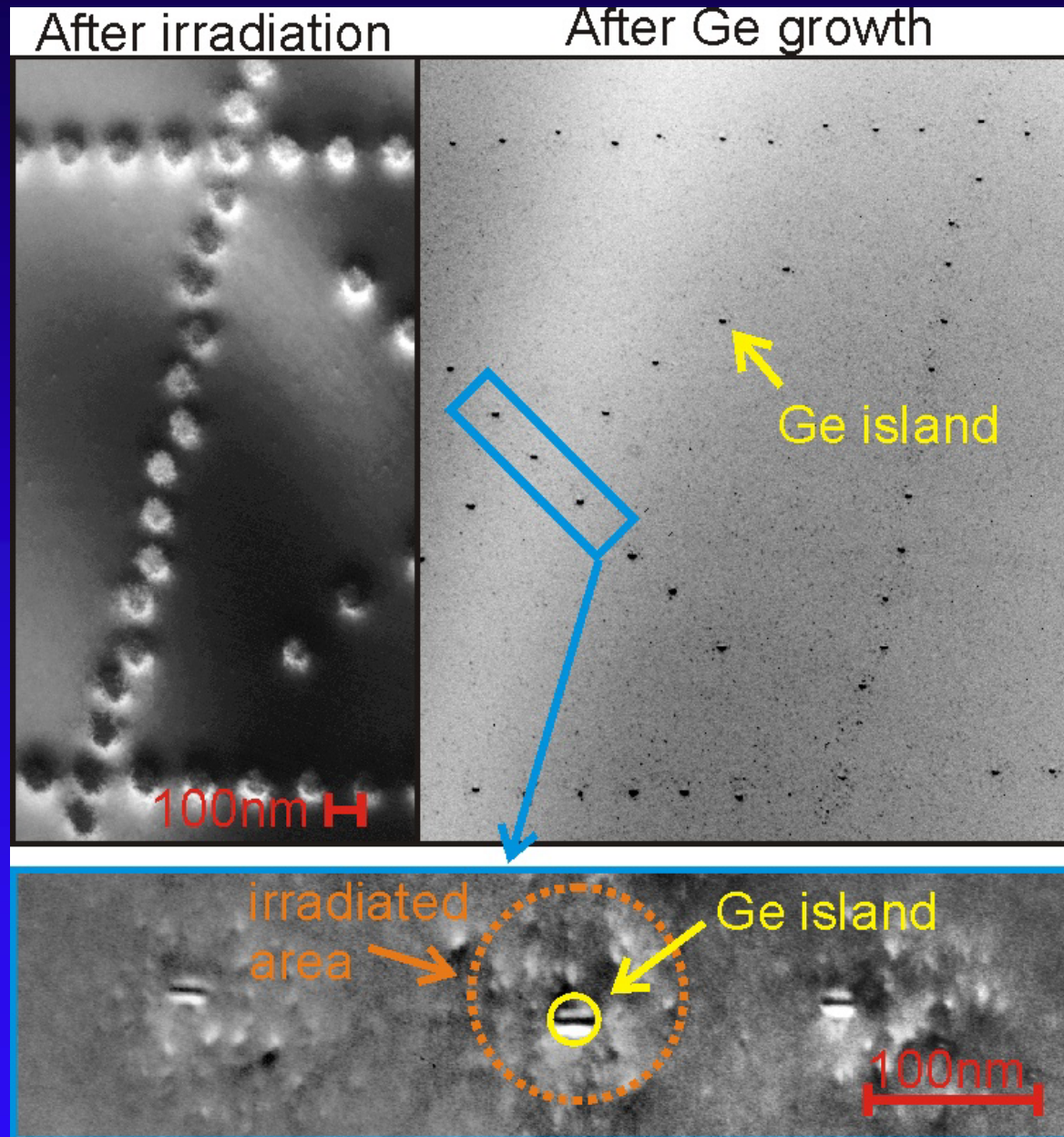
Branched PbSe Nanowires with High Surface Area



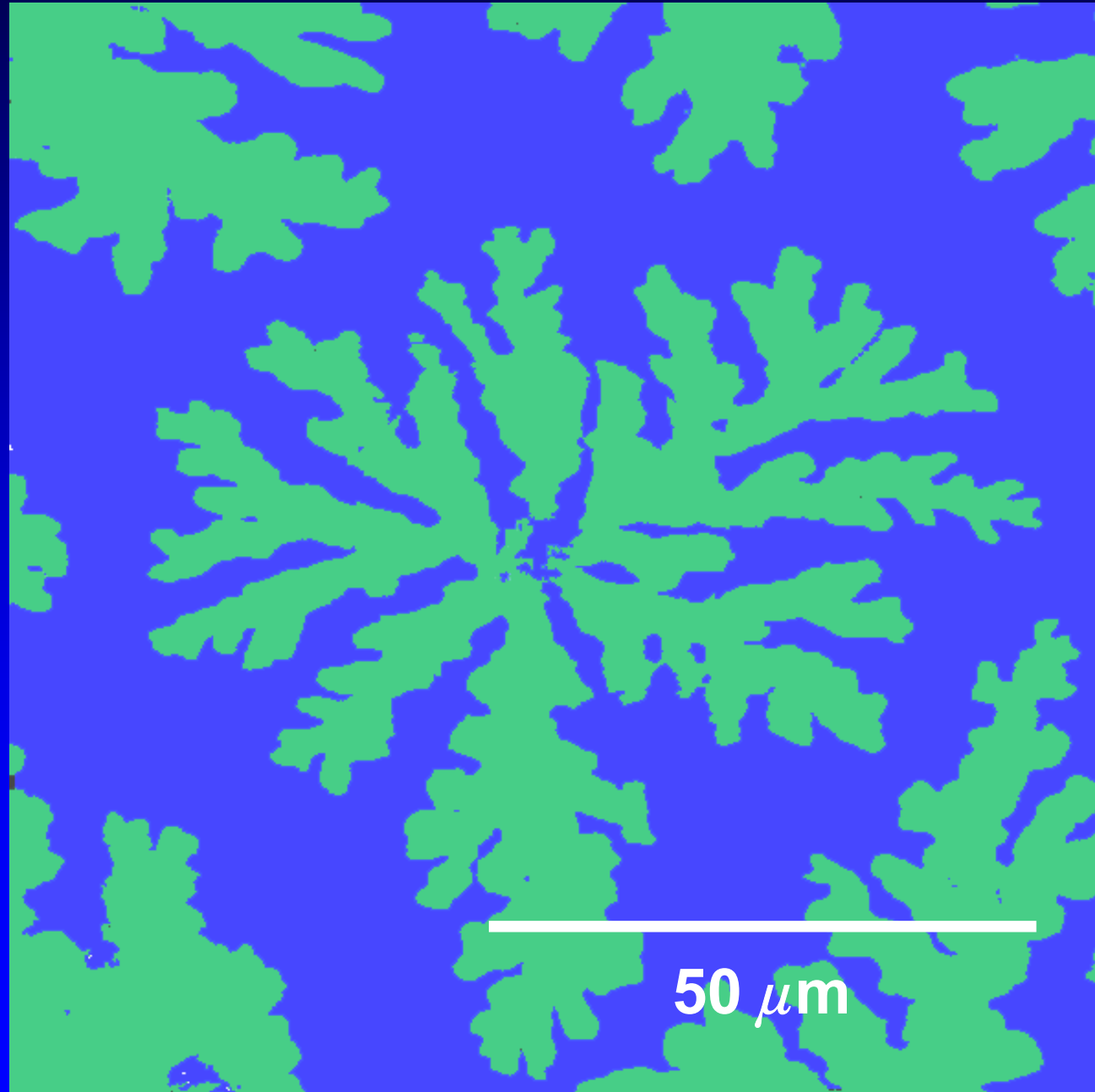
Self-assembly: SiGe Quantum Dots



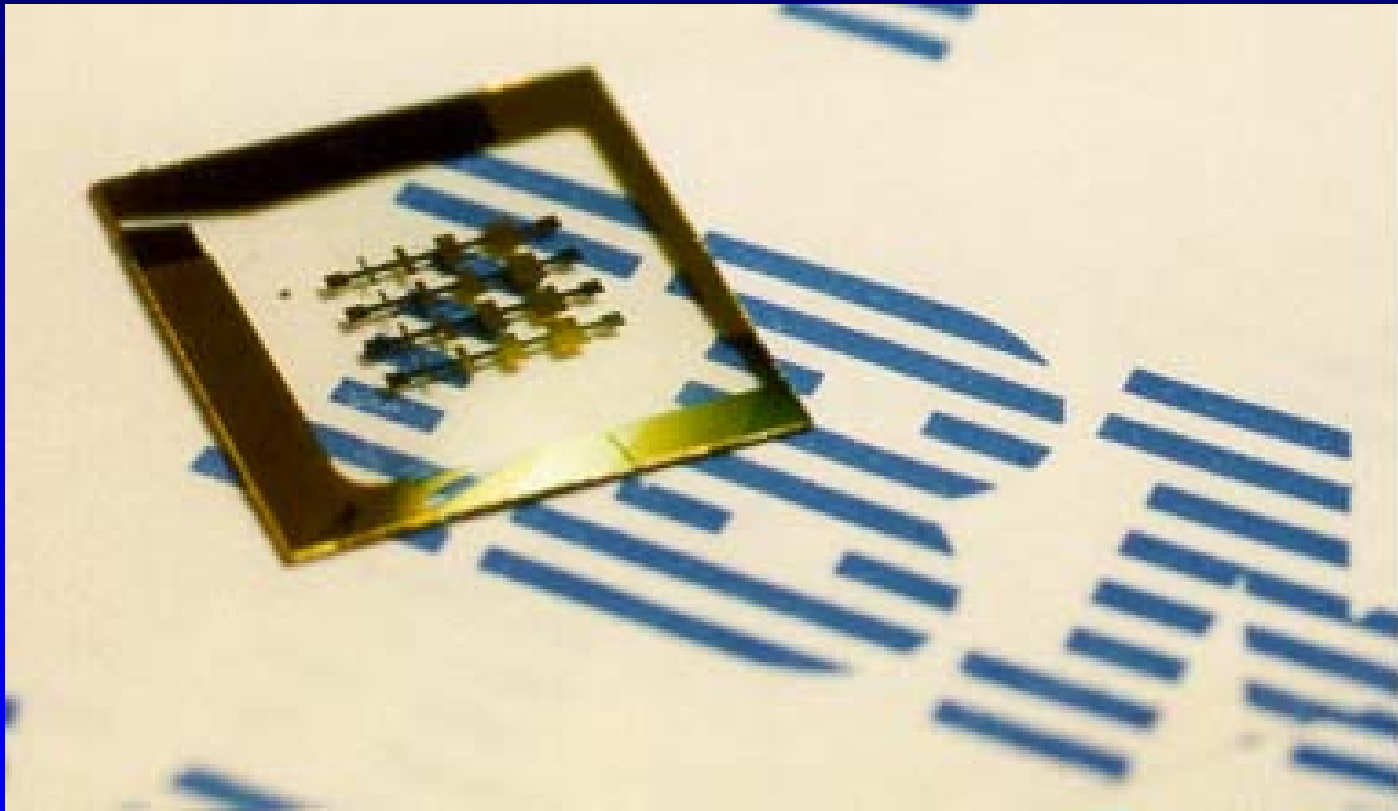
Precise Placement of Quantum Dots



Self Assembly: A One-Monlayer-Thick Pentacene “Snowflake”

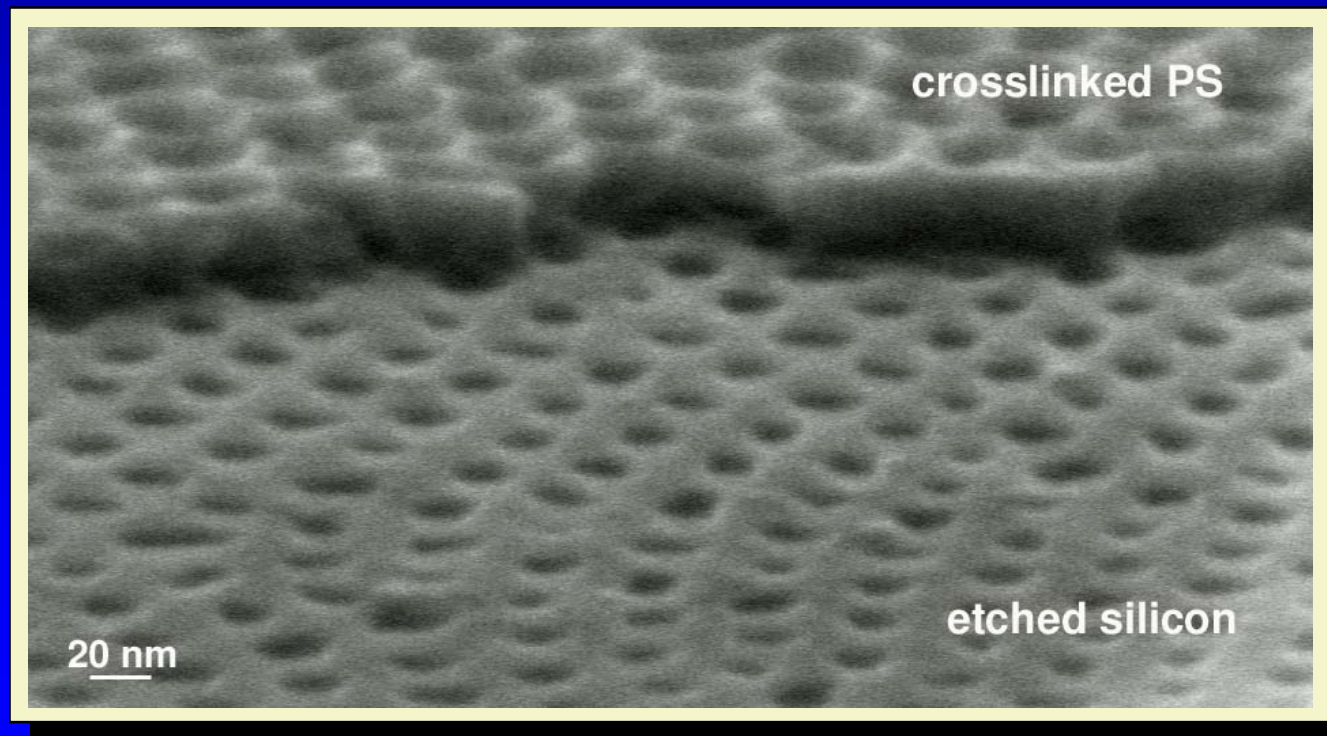
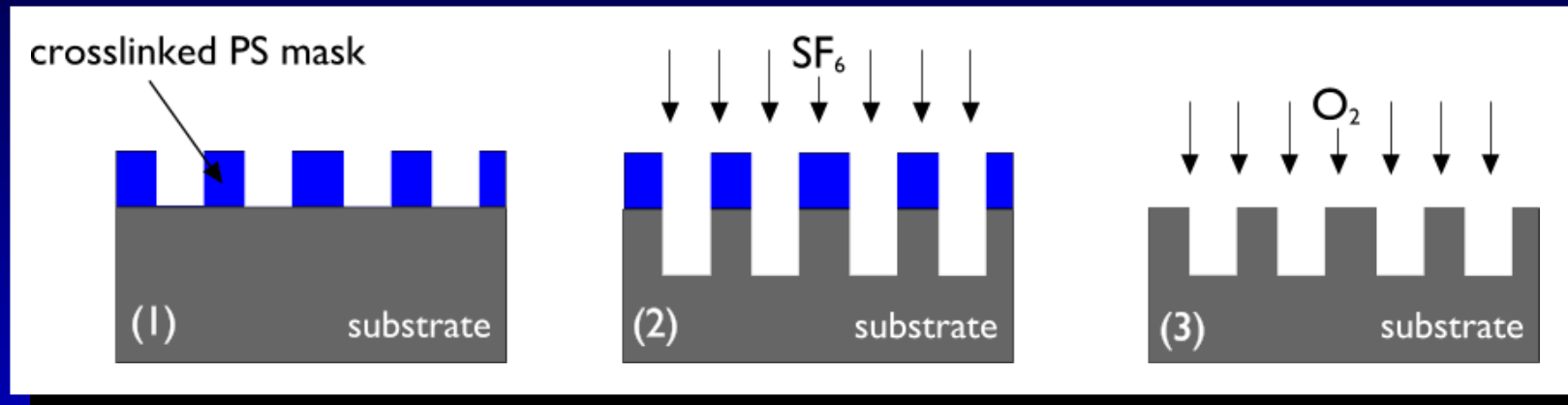


Thin Film Transistors on Transparent Plastic:

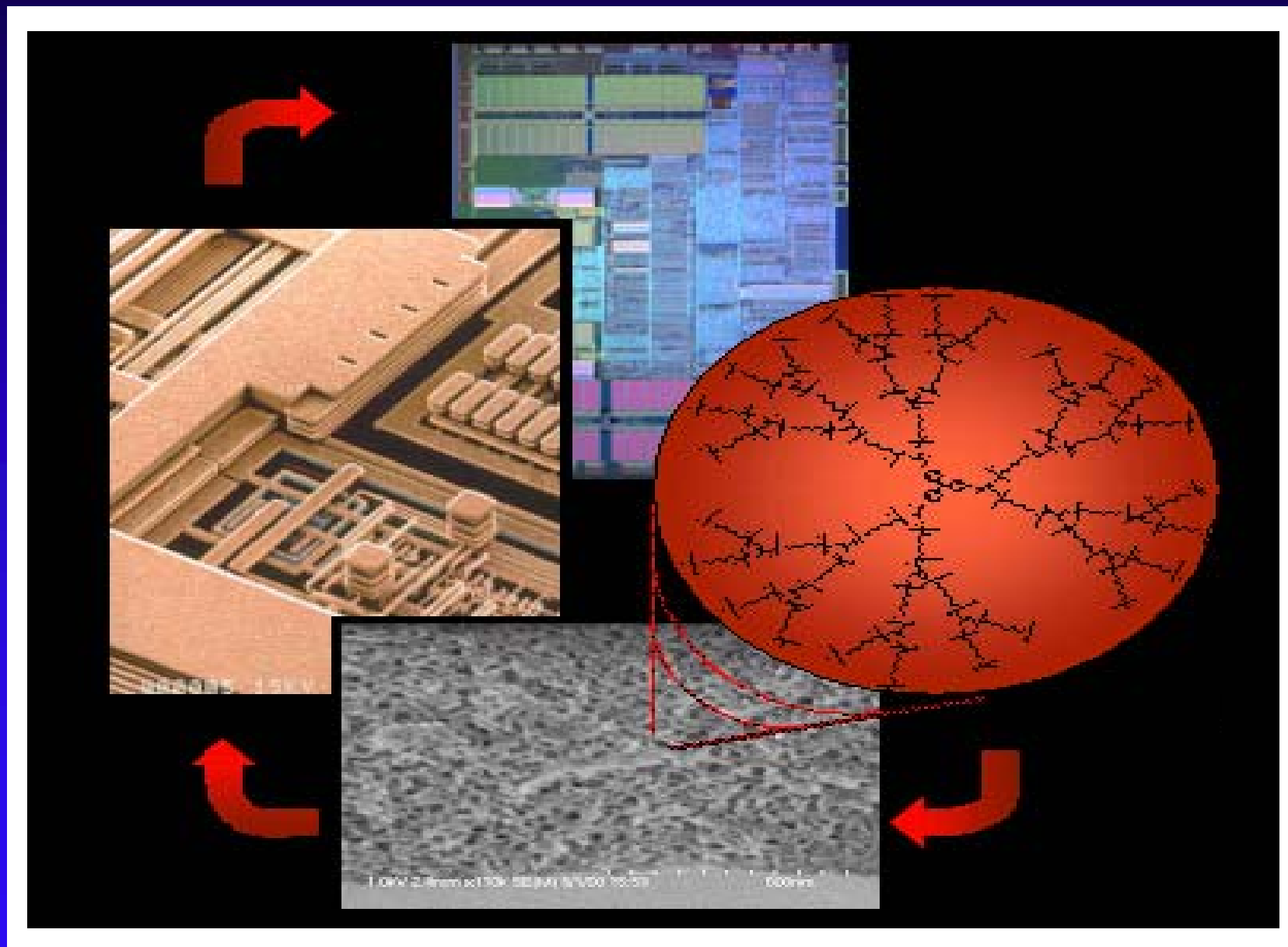


$\mu = 0.2$ to $0.4 \text{ cm}^2 \text{ V}^{-1}\text{s}^{-1}$, operating voltage 0 to 4 V.
All fabrication processes done at room temperature.

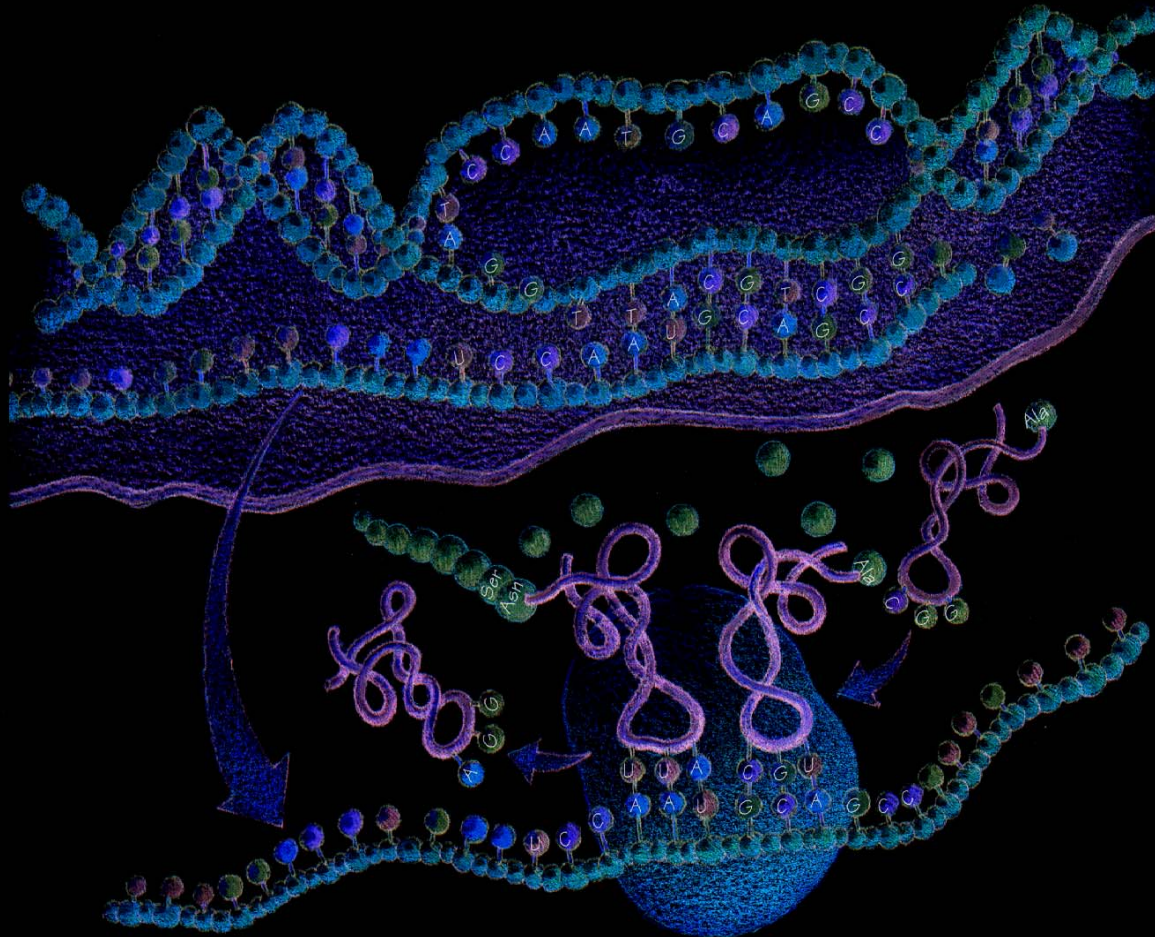
Patterning Silicon with Block Co-polymers



Porous Dielectrics for On-Chip Wiring



How much digital information will specify the structure?



Drawing from: "To Know Ourselves," US Dept. of Energy and The Human Genome Project 1996.



A living thing
(Paramecium)

How much digital information is needed to BUILD the structure?

- Microprocessor – Gigabytes
- Living Thing – Megabytes!

Nanotechnology ...

The ability to design and control the structure of an object on all length scales, from the atomic to the macroscopic.

Nanotechnology: We're just getting started.

